

# Zainuriah Hassan

## List of Publications by Year in Descending Order

**Source:** <https://exaly.com/author-pdf/7373968/zainuriah-hassan-publications-by-year.pdf>

**Version:** 2024-04-25

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

535  
papers

6,068  
citations

37  
h-index

54  
g-index

598  
ext. papers

6,846  
ext. citations

2.7  
avg, IF

6.29  
L-index

#	Paper	IF	Citations
535	Realization of UV-C absorption in ZnO nanostructures using fluorine and silver co-doping. <i>Colloids and Interface Science Communications</i> , <b>2022</b> , 47, 100588	5.4	1
534	Recent advances and challenges in the MOCVD growth of indium gallium nitride: A brief review. <i>Materials Science in Semiconductor Processing</i> , <b>2022</b> , 143, 106545	4.3	3
533	Synergetic effects of monoethanolamine (MEA) and post-deposition calcination on biosynthesized CeO <sub>2</sub> nanostructures spin-coated on silicon substrate. <i>Materials Chemistry and Physics</i> , <b>2022</b> , 278, 125656	4.4	0
532	A review of laser ablation and dicing of Si wafers. <i>Precision Engineering</i> , <b>2022</b> , 73, 377-408	2.9	2
531	Analysis using a two-layer model of the transport properties of InGaN epilayers grown on GaN template substrate. <i>Materials Science in Semiconductor Processing</i> , <b>2022</b> , 144, 106614	4.3	0
530	Investigation on the effect of vacuum annealing time on structural and optical properties of YAG:Ce nanoparticles prepared by mixed-fuel microwave solution combustion synthesis. <i>Optics and Laser Technology</i> , <b>2022</b> , 154, 108296	4.2	0
529	Improvement of Porous GaN-Based UV Photodetector with Graphene Cladding. <i>Applied Sciences (Switzerland)</i> , <b>2021</b> , 11, 10833	2.6	1
528	Growth of Polycrystalline Gallium Oxide Films in Stagnant Oxygen Stream Ambient. <i>Journal of Materials Research and Technology</i> , <b>2021</b> , 16, 139-139	5.5	0
527	The Effect of Medium Inhomogeneity in Modeling Underwater Optical Wireless Communication. <i>Journal of Communications</i> , <b>2021</b> , 386-393	0.5	1
526	Development of EGFET-based ITO pH sensors using epoxy free membrane. <i>Semiconductor Science and Technology</i> , <b>2021</b> , 36, 045027	1.8	2
525	Effect of indium pre-flow on wavelength shift and crystal structure of deep green light emitting diodes. <i>Optical Materials Express</i> , <b>2021</b> , 11, 926	2.6	2
524	Tailoring In <sub>2</sub> Ga <sub>2</sub> ZnO <sub>7</sub> thin film properties by annealing time effect. <i>Materials Chemistry and Physics</i> , <b>2021</b> , 262, 124281	4.4	
523	Comparative studies of metal-organic decomposed GaxCeyOz and CeO <sub>2</sub> based functional MOS capacitor. <i>International Journal of Energy Research</i> , <b>2021</b> , 45, 18257-18261	4.5	0
522	Effects of post-deposition annealing temperature in nitrogen/oxygen/nitrogen ambient on polycrystalline gallium oxide films. <i>Applied Surface Science</i> , <b>2021</b> , 550, 149340	6.7	6
521	Effect of etching time onto structural, morphological, and optical characteristics of quaternary AlInGaN films on Si substrate. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2021</b> , 263, 114911	3.1	1
520	Comparative study of oxidizing ambient infused with varying nitrogen flow rates for fabrication of ternary nitrided AlZrO based MOS capacitor. <i>International Journal of Energy Research</i> , <b>2021</b> , 45, 3838-3851	4.5	2
519	Novel SnO <sub>2</sub> -coated EGa <sub>2</sub> O <sub>3</sub> nanostructures for room temperature hydrogen gas sensor. <i>International Journal of Hydrogen Energy</i> , <b>2021</b> , 46, 7000-7010	6.7	14

518	The dependence of indium incorporation on specified temperatures in growing InGaN/GaN heterostructure using MOCVD technique. <i>Materials Research Bulletin</i> , <b>2021</b> , 137, 111176	5.1	2
517	Rapid synthesis of Ce <sup>3+</sup> :YAG via CO <sub>2</sub> laser irradiation combustion method: Influence of Ce doping and thickness of phosphor ceramic on the performance of a white LED device. <i>Journal of Solid State Chemistry</i> , <b>2021</b> , 294, 121866	3.3	5
516	Femtosecond laser dicing of ultrathin Si wafers with Cu backside layer - A fracture strength and microstructural study. <i>Journal of Manufacturing Processes</i> , <b>2021</b> , 62, 859-872	5	1
515	Effects of V/III ratio of InGaN quantum well at high growth temperature for near ultraviolet light emitting diodes. <i>Microelectronics International</i> , <b>2021</b> , 38, 119-126	0.8	0
514	The role of growth temperature on the indium incorporation process for the MOCVD growth of InGaN/GaN heterostructures. <i>Microelectronics International</i> , <b>2021</b> , 38, 105-112	0.8	1
513	Effects of three-step magnesium doping in p-GaN layer on the properties of InGaN-based light-emitting diode. <i>Microelectronics International</i> , <b>2021</b> , 38, 127-134	0.8	0
512	Investigation on structural, morphological, optical, and current-voltage characteristics of polyfluorene with dissimilar composition spin coated on ITO. <i>Optik</i> , <b>2021</b> , 242, 167034	2.5	3
511	High quality aluminum nitride layer grown with a combined step of nitridation and trimethylaluminum preflow. <i>Thin Solid Films</i> , <b>2021</b> , 736, 138915	2.2	0
510	Self-powered UV photodetector performance optimization based on Ag nanoparticles-encapsulated-ZnO nanorods by photo-deposition method. <i>Sensors and Actuators A: Physical</i> , <b>2021</b> , 331, 113032	3.9	4
509	Fabrication of ultra-violet photodetector with enhanced optoelectronic parameters using low-cost F-doped ZnO nanostructures. <i>Sensors and Actuators A: Physical</i> , <b>2021</b> , 332, 113092	3.9	3
508	High conversion and quantum efficiency indium-rich p-InGaN/p-InGaN/n-InGaN solar cell. <i>Physica B: Condensed Matter</i> , <b>2021</b> , 622, 413339	2.8	2
507	Enhanced sensitivity of low-cost fabricated fluorine doped ZnO metal semiconductor metal photodetector. <i>Optical Materials</i> , <b>2021</b> , 122, 111771	3.3	1
506	Study of the Effect of Injection Currents on White Light Emission of Ce-Doped YAG Phosphor Powder Prepared by Microwave Combustion. <i>Solid State Phenomena</i> , <b>2020</b> , 301, 60-68	0.4	1
505	Effect of annealing temperature on physical and electrical properties of solution-processed polycrystalline In <sub>2</sub> Ga <sub>2</sub> ZnO <sub>7</sub> thin film. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2020</b> , 31, 9705-9718	2.4	4
504	Chromaticity Properties of Curcuminoids Dye Nanofibers Prepared by Electrospinning for White Light Down-Conversion. <i>Solid State Phenomena</i> , <b>2020</b> , 301, 77-84	0.4	
503	High-k La <sub>x</sub> Ce <sub>y</sub> O <sub>z</sub> for Passivation of Si Substrate. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012030.	3	
502	Surface passivation via two-step grown nitrogen infused oxidation derived quaternary Al <sub>x</sub> Zr <sub>1-x</sub> O <sub>y</sub> N <sub>z</sub> . <i>Materials Letters</i> , <b>2020</b> , 276, 128175	3.3	
501	Ultraviolet electroluminescence from flowers-like n-ZnO nanorods/p-GaN light-emitting diode fabricated by modified chemical bath deposition. <i>Journal of Luminescence</i> , <b>2020</b> , 226, 117510	3.8	10

500	Fabrication of Deep Green Light Emitting Diode on Bulk Gallium Nitride Substrate. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012016	0.3	1
499	The Effect of Needle Diameter on Optical Properties and Morphological Structure of La <sub>2</sub> O <sub>3</sub> - PVA Phosphor Nanofibers Prepared by Electrospinning Method. <i>Solid State Phenomena</i> , <b>2020</b> , 301, 18-26	0.4	
498	On the Investigations of Chip-on-Board Ultra-Violet Sensor by Screen Printing of GaN Powder. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012015	0.3	
497	Effect of microwave time on the structural and luminescence properties of YAG:Ce prepared by microwave solution combustion (MSC) synthesis. <i>Optik</i> , <b>2020</b> , 212, 164437	2.5	5
496	Effect of Substrates on Structural, Morphological, Optical and Electrical Characteristics on Poly (9,9-di-n-octylfluorenyl-2,7-diyl) (PFO) Thin Films. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 026002	2	3
495	Mechanism study of SiO <sub>2</sub> layer formation and separation at the Si die sidewall during nanosecond laser dicing of ultrathin Si wafers with Cu backside layer. <i>Applied Physics A: Materials Science and Processing</i> , <b>2020</b> , 126, 1	2.6	2
494	Morphological and Structural Properties of Sol-Gel Derived ZnO Thin Films Spin-Coated on Different Substrates. <i>Solid State Phenomena</i> , <b>2020</b> , 301, 35-42	0.4	1
493	High temperature growth of aluminium doped zirconium oxide via post-sputter oxidation of Al <sub>2</sub> O <sub>3</sub> films with different composition. <i>Journal of Alloys and Compounds</i> , <b>2020</b> , 813, 152206	5.7	1
492	Dual-step grown ternary aluminium zirconium oxide and its characteristics for metal-oxide-semiconductor capacitor. <i>Ceramics International</i> , <b>2020</b> , 46, 10416-10424	5.1	4
491	Simultaneous two-step assisted growth of aluminium zirconium oxide from Al <sub>2</sub> O <sub>3</sub> films. <i>Ceramics International</i> , <b>2020</b> , 46, 297-306	5.1	4
490	Assessment of structural, morphological and optical properties of ZnO thin films grown by physical and chemical techniques. <i>Materials Today: Proceedings</i> , <b>2020</b> , 21, 1022-1025	1.4	
489	Performance of polycrystalline GaN based metal-semiconductor-metal (MSM) photodetector with different contact. <i>Superlattices and Microstructures</i> , <b>2020</b> , 138, 106369	2.8	7
488	Effect of zinc acetate dihydrate concentration on morphology of ZnO seed layer and ZnO nanorods grown by hydrothermal method. <i>Colloids and Interface Science Communications</i> , <b>2020</b> , 38, 100312	5.4	18
487	Effects of Post-Deposition Annealing Time in Forming Gas Ambient on Y <sub>2</sub> O <sub>3</sub> Films Deposited on Silicon Substrate. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012031	0.3	
486	Synthesis and Characterization of YAG:Ce Phosphor by Microwave Induced Combustion Synthesis with Different Fuel Sources. <i>Solid State Phenomena</i> , <b>2020</b> , 301, 69-76	0.4	1
485	Growth and Characterization of Ternary Hf Ta O Films via Nitrogen-Infused Wet Oxidation. <i>ACS Omega</i> , <b>2020</b> , 5, 26347-26356	3.9	1
484	Ce-doped YAG single-crystals prepared by continuous wave (CW) CO <sub>2</sub> laser combustion technique with attractive characteristics and moderate white LED performance. <i>Optics and Laser Technology</i> , <b>2020</b> , 132, 106506	4.2	4
483	Preparation and characterisation of aluminium zirconium oxide for metal-oxide-semiconductor capacitor. <i>International Journal of Energy Research</i> , <b>2020</b> , 44, 10562-10575	4.5	1

482	Enhancing Performance of Porous Si-Doped GaN Based MSM Photodetector Using 50 Hz ACPEC. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012006	0.3	0
481	Effect of varying thermal annealing temperatures on the surface and electrical properties of Mg-doped GaN. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012045	0.3	
480	Growth evolution and customized attributes of catalyst-free ZnO nanowires: role of varied Ar/O <sub>2</sub> flow rate. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2020</b> , 31, 17422-17431	2.1	
479	Structural and Optical Properties of Nanofibers Prepared with Electrospinning by Using PMMA Integrated with Curcuminoids to Produce White LED. <i>Fibers and Polymers</i> , <b>2020</b> , 21, 1733-1742	2	1
478	Luminescence Characteristics of Hybridized Polyfluorene. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1535, 012055	0.3	
477	Synthesis of Architectural-Cubic Porous Silicon by Electroless Stain Etching in V <sub>2</sub> O <sub>5</sub> and HF Solution. <i>Silicon</i> , <b>2020</b> , 12, 1761-1768	2.4	
476	Laser annealing enhanced the photophysical performance of Pt/n-PSi/ZnO/Pt-based photodetectors. <i>Solid-State Electronics</i> , <b>2020</b> , 171, 107821	1.7	1
475	Structural, morphological, optical, and gas sensing characteristics of ultraviolet-assisted photoelectrochemical etching derived AlInGaN nano-spikes. <i>Journal of Materials Research and Technology</i> , <b>2019</b> , 8, 2767-2776	5.5	5
474	Fracture strength and microstructural study of ultrathin Si die with Cu backside layer diced with picosecond laser. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , <b>2019</b> , 759, 785-796	5.3	2
473	Effect Grinding of Graphite on Structural and Morphological Characteristics of Carbon Nanotubes Grown by Microwave Oven. <i>Solid State Phenomena</i> , <b>2019</b> , 290, 122-126	0.4	2
472	Aluminum Nitride Thin Films Grown by Sol-Gel Spin Coating Technique. <i>Solid State Phenomena</i> , <b>2019</b> , 290, 137-141	0.4	1
471	Fabrication of In <sub>x</sub> Ga <sub>1-x</sub> N/GaN Multi-Quantum well Structure for Green Light Emitting Diode on Patterned Sapphire Substrate by Metal Organic Chemical Vapour Deposition. <i>Solid State Phenomena</i> , <b>2019</b> , 290, 147-152	0.4	1
470	Growth Temperature Dependence of Sol-Gel Spin Coated Indium Nitride Thin Films. <i>Solid State Phenomena</i> , <b>2019</b> , 290, 153-159	0.4	1
469	Chromaticity Study of Curcumin Dye Extracted from Curcuma longa L. Using for UV Light down Conversion for White Light Emitting Diode. <i>Solid State Phenomena</i> , <b>2019</b> , 290, 183-189	0.4	
468	Improving polycrystalline GaN by controlling annealing temperature of ScN interlayer. <i>Materials Research Express</i> , <b>2019</b> , 6, 066403	1.7	
467	Passivation of silicon substrate using two-step grown ternary aluminium doped zirconium oxide. <i>Applied Surface Science</i> , <b>2019</b> , 493, 411-422	6.7	11
466	Optimization of Precursor Concentration for the Fabrication of V <sub>2</sub> O <sub>5</sub> Nanorods and their MSM Photodetector on Silicon Substrate. <i>Journal of Electronic Materials</i> , <b>2019</b> , 48, 5640-5649	1.9	1
465	Fabrication of AlN/GaN MSM photodetector with platinum as schottky contacts. <i>Materials Research Express</i> , <b>2019</b> , 6, 115913	1.7	2

464	A novel porous silicon multi-ions selective electrode based extended gate field effect transistor for sodium, potassium, calcium, and magnesium sensor. <i>Applied Physics A: Materials Science and Processing</i> , <b>2019</b> , 125, 1	2.6	7
463	Study of efficient semipolar (11-22) InGaN green micro-light-emitting diodes on high-quality (11-22) GaN/sapphire template. <i>Optics Express</i> , <b>2019</b> , 27, 24154-24160	3.3	31
462	Investigation of sintering temperature and Ce <sup>3+</sup> concentration in YAG:Ce phosphor powder prepared by microwave combustion for white-light-emitting diode luminance applications. <i>Materials Chemistry and Physics</i> , <b>2019</b> , 229, 22-31	4.4	10
461	Sol-gel-derived gallium nitride thin films for ultraviolet photodetection. <i>Microelectronics International</i> , <b>2019</b> , 36, 8-13	0.8	3
460	A two-step growth route of ternary aluminium doped zirconium oxide film on silicon. <i>Journal of Alloys and Compounds</i> , <b>2019</b> , 777, 736-748	5.7	12
459	Structural and optical properties of AlN/GaN and AlN/AlGaIn/GaN thin films on silicon substrate prepared by plasma assisted molecular beam epitaxy (MBE). <i>Results in Physics</i> , <b>2019</b> , 12, 1177-1181	3.7	6
458	Catalytic Growth of 1D ZnO Nanoneedles on Glass Substrates Through Vapor Transport. <i>Journal of Electronic Materials</i> , <b>2019</b> , 48, 1660-1668	1.9	3
457	Effects of ultraviolet-assisted electrochemical etching current densities on structural and optical characteristics of porous quaternary AlInGaIn alloys. <i>Arabian Journal of Chemistry</i> , <b>2019</b> , 12, 3417-3430	5.9	11
456	Enhancement of optical transmittance and electrical resistivity of post-annealed ITO thin films RF sputtered on Si. <i>Applied Surface Science</i> , <b>2018</b> , 443, 544-547	6.7	59
455	High-performance nanoporous silicon-based photodetectors. <i>Optik</i> , <b>2018</b> , 168, 424-431	2.5	5
454	Influence of ammonia flow rate for improving properties of polycrystalline GaN. <i>Superlattices and Microstructures</i> , <b>2018</b> , 118, 130-136	2.8	2
453	Growth and characterization of GaN nanostructures under various ammoniating time with fabricated Schottky gas sensor based on Si substrate. <i>Superlattices and Microstructures</i> , <b>2018</b> , 117, 92-104	2.8	11
452	An improved three-point bending test method for the investigation of nanosecond laser dicing of ultrathin Si dies with Cu stabilization layer. <i>Materials Characterization</i> , <b>2018</b> , 136, 29-40	3.9	6
451	Fabrication and characterization of copper doped zinc oxide by using Co-sputtering technique. <i>Materials Research Bulletin</i> , <b>2018</b> , 97, 314-318	5.1	8
450	Effects of coating cycles on spin-coated indium nitride thin films. <i>Surface Engineering</i> , <b>2018</b> , 34, 554-561	2.6	2
449	Effects of ZnO seed layer thickness on catalyst-free growth of ZnO nanostructures for enhanced UV photoresponse. <i>Optics and Laser Technology</i> , <b>2018</b> , 98, 344-353	4.2	29
448	Influence of growth temperature and duration on different properties of ultra-long ZnO nanorods grown by modified chemical bath deposition method. <i>Materials Research Express</i> , <b>2018</b> , 5, 095020	1.7	3
447	Porous Formation in p-Type Gallium Nitride Films via 50 Hz Operated Alternating Current-Assisted Photo-Electrochemical Etching in Methanol-Sulfuric Acid Solution. <i>Journal of the Electrochemical Society</i> , <b>2018</b> , 165, H620-H628	3.9	5

446	A High-Sensitivity Hydrogen Gas Sensor Based on Carbon Nanotubes Fabricated on Glass Substrate. <i>Journal of Electronic Materials</i> , <b>2018</b> , 47, 6671-6680	1.9	11
445	Photophysical performance of radio frequency sputtered Pt/n-PSi/ZnO NCs/Pt photovoltaic photodetectors. <i>Optical Materials</i> , <b>2018</b> , 84, 830-842	3.3	5
444	Photoelectrochemical ultraviolet photodetector by anodic titanium dioxide nanotube layers. <i>Sensors and Actuators A: Physical</i> , <b>2018</b> , 279, 263-271	3.9	11
443	Effect of Annealing Time of YAG:Ce <sup>3+</sup> Phosphor on White Light Chromaticity Values. <i>Journal of Electronic Materials</i> , <b>2018</b> , 47, 1638-1646	1.9	17
442	The Effect of The Wavelength of the LED used to Pump Phosphor Produced from Curcuminoids Dye Extracted from Turmeric ( <i>Curcuma Longa</i> L.) to Produce White Light. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2018</b> , 454, 012048	0.4	2
441	Optical and structural properties of curcuminoids extracted from <i>Curcuma longa</i> L. for hybrid white light diode. <i>EPJ Applied Physics</i> , <b>2018</b> , 84, 10501	1.1	4
440	Optical Properties and UV Sensing Response of Nitrogen-doped TiO <sub>2</sub> Thin Film by CVD. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 1083, 012025	0.3	
439	Effect of Different UV Light Intensity on Porous Silicon Fabricated by Using Alternating Current Photo-Assisted Electrochemical Etching (ACPEC) Technique. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 1083, 012034	0.3	1
438	Structural, Electrical and Optical Properties of Sputtered-Grown InN Films on ZnO Buffered Silicon, Bulk GaN, Quartz and Sapphire Substrates. <i>Journal of Electronic Materials</i> , <b>2018</b> , 47, 4875-4881	1.9	4
437	Influences of elevated thermal decomposition of ammonia gas on indium nitride grown by sol-gel spin coating method. <i>Materials Research Bulletin</i> , <b>2017</b> , 96, 258-261	5.1	4
436	A novel CuS thin film deposition method by laser-assisted spray photolysis deposition and its application to EGFET. <i>Sensors and Actuators B: Chemical</i> , <b>2017</b> , 247, 197-215	8.5	11
435	Using Deionized Water with Ethanol as a Solvent of CuS EGFET as pH Sensor. <i>Materials Science Forum</i> , <b>2017</b> , 886, 37-41	0.4	1
434	Electrochemical growth of controlled tip shapes of ZnO nanorod arrays on silicon substrate and enhanced photoluminescence emission from nanopyramid arrays compared with flat-head nanorods. <i>Optical Materials</i> , <b>2017</b> , 72, 276-282	3.3	5
433	Laser-induced solution combustion of nano-Y <sub>2</sub> O <sub>3</sub> :0.04Ce phosphors and their fluorescent properties for white light conversion. <i>Journal of Alloys and Compounds</i> , <b>2017</b> , 711, 42-50	5.7	13
432	A comparative study of InN growth on quartz, silicon, C-sapphire and bulk GaN substrates by RF magnetron sputtering. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2017</b> , 28, 9228-9236	2.1	6
431	Growth mechanism of seed/catalyst-free zinc oxide nanowire balls using intermittently pumped carrier gas: Synthesis, characterization and applications. <i>Optical Materials</i> , <b>2017</b> , 67, 70-77	3.3	4
430	Influences of substrate type on the pH sensitivity of CuS thin films EGFET prepared by spray pyrolysis deposition. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 63, 269-278	4.3	22
429	Fabrication and characterization of AlN metal-insulator-semiconductor grown Si substrate. <i>Modern Physics Letters B</i> , <b>2017</b> , 31, 1750313	1.6	0

428	Effect of ferrocene catalyst particle size on structural and morphological characteristics of carbon nanotubes grown by microwave oven. <i>Journal of Materials Science</i> , <b>2017</b> , 52, 12772-12782	4.3	4
427	Effect of temperature on hydrothermally grown high-quality single-crystals Mg-doped ZnO nanorods for light-emitting diode application. <i>Journal of Luminescence</i> , <b>2017</b> , 192, 634-643	3.8	15
426	Cost-effective single-step carbon nanotube synthesis using microwave oven. <i>Materials Research Express</i> , <b>2017</b> , 4, 085602	1.7	13
425	Sputtered growth of high mobility InN thin films on different substrates using Cu-ZnO buffer layer. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 71, 166-173	4.3	9
424	The effect of etching duration on structural properties of porous Si fabricated by a new two-steps alternating current photo-assisted electrochemical etching (ACPEC) technique for MSM photodetector <b>2017</b> ,		4
423	Influence of CuS membrane annealing time on the sensitivity of EGFET pH sensor. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 71, 217-225	4.3	19
422	Fabrication of Cu <sub>2</sub> O nanocrystalline thin films photosensor prepared by RF sputtering technique. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2017</b> , 94, 132-138	3	12
421	Photo-electrochemically synthesized light emitting nanoporous silicon based UV photodetector: influence of current density. <i>Materials Research Express</i> , <b>2017</b> , 4, 116203	1.7	5
420	Sensitivity of CuS Membrane pH Sensor With and Without MOSFET. <i>Jom</i> , <b>2017</b> , 69, 1134-1142	2.1	9
419	Deposition of a polycrystalline GaN layer on a porous Si/Si substrate by an electron beam evaporator with a successive ammonia annealing treatment. <i>Journal of Alloys and Compounds</i> , <b>2017</b> , 690, 397-402	5.7	6
418	High sensitivity extended gate effect transistor based on V <sub>2</sub> O <sub>5</sub> nanorods. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2017</b> , 28, 1364-1369	2.1	14
417	Catalytic growth of one-dimensional single-crystalline ZnO nanostructures on glass substrate by vapor transport. <i>Ceramics International</i> , <b>2017</b> , 43, 610-616	5.1	10
416	Effects of ammonia-ambient annealing on physical and electrical characteristics of rare earth CeO <sub>2</sub> as passivation film on silicon. <i>Journal of Alloys and Compounds</i> , <b>2017</b> , 695, 3104-3115	5.7	20
415	Effects of Concentration and Substrate Type on Structure and Conductivity of p-Type CuS Thin Films Grown by Spray Pyrolysis Deposition. <i>Journal of Electronic Materials</i> , <b>2017</b> , 46, 218-225	1.9	7
414	Fabrication and characterization of metal-semiconductor-metal ultraviolet photodetector based on rutile TiO <sub>2</sub> nanorod. <i>Materials Research Bulletin</i> , <b>2016</b> , 73, 29-37	5.1	44
413	Sensitivity of CuS and CuS/ITO EGFETs implemented as pH sensors. <i>Applied Physics A: Materials Science and Processing</i> , <b>2016</b> , 122, 1	2.6	15
412	Behavior of Etching Process on Formation of Porous Polycrystalline GaN Layer through Electroless Etching. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, P584-P589	2	2
411	Fabrication and characterization of V <sub>2</sub> O <sub>5</sub> nanorods based metal-semiconductor-metal photodetector. <i>Sensors and Actuators A: Physical</i> , <b>2016</b> , 250, 250-257	3.9	63



410	A high-sensitivity, fast-response, rapid-recovery UV photodetector fabricated based on catalyst-free growth of ZnO nanowire networks on glass substrate. <i>Optical Materials</i> , <b>2016</b> , 60, 30-37	3.3	67
409	Synthesis and characterization of nanocrystalline CdS thin films for highly photosensitive self-powered photodetector. <i>EPJ Applied Physics</i> , <b>2016</b> , 74, 10101	1.1	14
408	Simulation of optimum parameters for GaN MSM UV photodetector <b>2016</b> ,		2
407	Catalyst-free growth of ZnO nanowires on ITO seed/glass by thermal evaporation method: Effects of ITO seed layer thickness <b>2016</b> ,		4
406	Surface Alteration of Planar P-Type Gallium Nitride to Porous Structure Using 50 Hz Alternating Current-Assisted Photo-Electrochemical Etching Route. <i>Journal of the Electrochemical Society</i> , <b>2016</b> , 163, H642-H651	3.9	6
405	Improved conductivity of indium-tin-oxide film through the introduction of intermediate layer. <i>Superlattices and Microstructures</i> , <b>2016</b> , 97, 202-211	2.8	4
404	Control growth of catalyst-free ZnO tetrapods on glass substrate by thermal evaporation method. <i>Ceramics International</i> , <b>2016</b> , 42, 13144-13150	5.1	6
403	Effect of Annealing on the Electrical Properties of CuxS Thin Films. <i>Procedia Chemistry</i> , <b>2016</b> , 19, 15-20		16
402	Annealing effects on polycrystalline GaN using nitrogen and ammonia ambients. <i>Superlattices and Microstructures</i> , <b>2016</b> , 97, 193-201	2.8	9
401	Fabrication of a highly flexible low-cost H <sub>2</sub> gas sensor using ZnO nanorods grown on an ultra-thin nylon substrate. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2016</b> , 27, 9461-9469	2.1	25
400	Free growth of one-dimensional Ga <sub>2</sub> O <sub>3</sub> nanostructures including nanowires, nanobelts and nanosheets using a thermal evaporation method. <i>Ceramics International</i> , <b>2016</b> , 42, 13343-13349	5.1	21
399	Room temperature hydrogen gas sensing characteristics of porous quaternary AlInGaN film prepared via UV-assisted photo-electrochemical etching. <i>Superlattices and Microstructures</i> , <b>2016</b> , 95, 65-70	2.8	2
398	INFLUENCE OF ANNEALING DURATION ON THE GROWTH OF V <sub>2</sub> O <sub>5</sub> NANORODS SYNTHESIZED BY SPRAY PYROLYSIS TECHNIQUE. <i>Surface Review and Letters</i> , <b>2016</b> , 23, 1650057	1.1	3
397	Broadband anti-reflective properties of grown ZnO nanopyramidal structure on Si substrate via low-temperature electrochemical deposition. <i>Ceramics International</i> , <b>2016</b> , 42, 5136-5140	5.1	7
396	Solvothermal preparation and characterization of ternary alloy CdS Se <sub>1-x</sub> nanowires. <i>Optik</i> , <b>2016</b> , 127, 1962-1966	2.5	3
395	Structural and optical investigation of porous quaternary Al <sub>0.10</sub> In <sub>0.10</sub> Ga <sub>0.80</sub> N films produced via ultraviolet-assisted photo-electrochemical etching in acidic solutions. <i>Journal of Alloys and Compounds</i> , <b>2016</b> , 662, 32-43	5.7	8
394	Large-scale uniform ZnO tetrapods on catalyst free glass substrate by thermal evaporation method. <i>Materials Research Bulletin</i> , <b>2016</b> , 79, 63-68	5.1	17
393	Characterization of V <sub>2</sub> O <sub>5</sub> nanorods grown by spray pyrolysis technique. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2016</b> , 27, 4613-4621	2.1	12

392	Effects of annealing temperature on optical, morphological, and electrical characteristics of polyfluorene-derivative thin films on ITO glass substrate. <i>Applied Optics</i> , <b>2016</b> , 55, 1198-205	0.2	6
391	Catalyst-free growth of ZnO nanowires on ITO seed layer/glass by thermal evaporation method: Effects of ITO seed layer laser annealing temperature. <i>Superlattices and Microstructures</i> , <b>2016</b> , 92, 68-79	2.8	21
390	Effect of nitrogen doping on structural, morphological, optical and electrical properties of radio frequency magnetron sputtered zinc oxide thin films. <i>Physica B: Condensed Matter</i> , <b>2016</b> , 490, 16-20	2.8	7
389	Effect of different EBL structures on deep violet InGaN laser diodes performance. <i>Optics and Laser Technology</i> , <b>2016</b> , 76, 106-112	4.2	17
388	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. <i>Applied Surface Science</i> , <b>2016</b> , 365, 296-305	6.7	8
387	NANOPOROUS GALLIUM NITRIDE THROUGH ANISOTROPIC METAL-ASSISTED ELECTROLESS PHOTOCHEMICAL WET ETCHING TECHNIQUE. <i>Surface Review and Letters</i> , <b>2016</b> , 23, 1550106	1.1	2
386	Effect of Light on the Sensitivity of CuS Thin Film EGFET Implemented as pH Sensor. <i>International Journal of Electrochemical Science</i> , <b>2016</b> , 4380-4388	2.2	13
385	Structural, Morphological and Electrical Properties of In-Doped Zinc Oxide Nanostructure Thin Films Grown on p-Type Gallium Nitride by Simultaneous Radio-Frequency Direct-Current Magnetron Co-Sputtering. <i>Chinese Physics Letters</i> , <b>2016</b> , 33, 066101	1.8	1
384	Preparation of high quality Mg doped ZnO nanorod arrays with enhanced optical properties by MgO passivation. <i>Optik</i> , <b>2016</b> , 127, 9250-9258	2.5	8
383	Porous Quaternary Al <sub>0.1</sub> In <sub>0.1</sub> Ga <sub>0.8</sub> N Film Formation via Photoelectrochemical Etching in HF:C <sub>2</sub> H <sub>5</sub> OH Electrolyte. <i>Journal of the American Ceramic Society</i> , <b>2016</b> , 99, 2395-2401	3.8	7
382	Hydrothermal growth and characterization of vertically well-aligned and dense ZnO nanorods on glass and silicon using a simple optimizer system <b>2016</b> ,		1
381	Hydrothermal synthesis of highly crystalline ZnO nanorod arrays: Dependence of morphology and alignment on growth conditions <b>2016</b> ,		2
380	CuS p- type thin film characterization deposited on Ti, ITO and glass substrates using spray pyrolysis deposition (SPD) for light emitting diode (LED) application <b>2016</b> ,		2
379	Fabrication of Tungsten Oxide Nanostructure by Sol-Gel Method. <i>Procedia Chemistry</i> , <b>2016</b> , 19, 113-118		14
378	Structural and optical properties of Si-doped Al <sub>0.08</sub> In <sub>0.08</sub> Ga <sub>0.84</sub> N thin films grown on different substrates for optoelectronic devices. <i>Superlattices and Microstructures</i> , <b>2016</b> , 95, 95-107	2.8	1
377	High figure of merit of the post-annealed Ti/Al/ITO transparent conductive contacts sputter deposited on n-GaN. <i>Journal of Alloys and Compounds</i> , <b>2016</b> , 681, 186-190	5.7	7
376	Dependence of output emission wavelength and LD performance on barriers material and thickness. <i>Optik</i> , <b>2016</b> , 127, 4815-4818	2.5	2
375	Investigation and Characterization of ZnO Nanostructures Synthesized by Electrochemical Deposition. <i>Procedia Chemistry</i> , <b>2016</b> , 19, 83-90		8

374	Performance evaluation of titanium dioxide based dye-sensitized solar cells under the influence of anodization steps, nanotube length and ionic liquid-free redox electrolyte solvents. <i>Superlattices and Microstructures</i> , <b>2016</b> , 94, 74-84	2.8	6
373	Visible Luminescence of Nanoporous Silicon Using Alternating Current Photo-Assisted Electrochemical Etching for Potential MSM Photodetector. <i>Materials Science Forum</i> , <b>2016</b> , 846, 274-282	0.4	
372	Structural and Optical Studies of Undoped Porous GaN Prepared by Pt-Assisted Electroless Etching. <i>Materials Science Forum</i> , <b>2016</b> , 846, 358-365	0.4	2
371	High performance CuS p-type thin film as a hydrogen gas sensor. <i>Sensors and Actuators A: Physical</i> , <b>2016</b> , 249, 68-76	3.9	40
370	Rapid Formation and Evolution of Anodized-Zn Nanostructures in NaHCO <sub>3</sub> Solution. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, M105-M112	2	18
369	Low-power UV photodetection characteristics of ZnO tetrapods grown on catalyst-free glass substrate. <i>Sensors and Actuators A: Physical</i> , <b>2016</b> , 250, 187-194	3.9	14
368	Identification and characteristics of core-shell ZnO/ZnO:Mg nanorods synthesized by hydrothermal method. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2016</b> , 27, 12618-12626	2.1	1
367	Investigation of structural and optical properties of GaN on flat and porous silicon. <i>Superlattices and Microstructures</i> , <b>2016</b> , 97, 586-590	2.8	11
366	High-performance p-n heterojunction photodetectors based on V <sub>2</sub> O <sub>5</sub> nanorods by spray pyrolysis. <i>Applied Physics A: Materials Science and Processing</i> , <b>2016</b> , 122, 1	2.6	21
365	Effects of Nitridation Temperature on Characteristics of Gallium Nitride Thin Films Prepared Via Two-Step Method. <i>Acta Metallurgica Sinica (English Letters)</i> , <b>2015</b> , 28, 362-366	2.5	5
364	Preparation of porous InAlGa <sub>N</sub> /Si(111) by photoelectrochemical etching for high performance hydrogen gas sensors at room temperature. <i>Sensors and Actuators B: Chemical</i> , <b>2015</b> , 213, 276-284	8.5	3
363	Fabrication of low cost UV photo detector using ZnO nanorods grown onto nylon substrate. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2015</b> , 26, 1322-1331	2.1	43
362	Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN/AlN heterostructures grown on Si(111) substrates by MBE for MSM UV photodetector applications. <i>Materials Science in Semiconductor Processing</i> , <b>2015</b> , 34, 214-223	4.3	15
361	Thermal Annealing Effect on Properties of Zn Foils Substrates. <i>Materials Science Forum</i> , <b>2015</b> , 819, 215-219		
360	Fabrication of titanium dioxide nanotubes in fluoride-free electrolyte via rapid breakdown anodization. <i>Journal of Porous Materials</i> , <b>2015</b> , 22, 1437-1444	2.4	12
359	Effect of using two-step thermal annealing with different ambient gas on Mg activation and crystalline quality in GaN. <i>Superlattices and Microstructures</i> , <b>2015</b> , 82, 592-598	2.8	7
358	Alteration of structural and optical properties in quaternary Al <sub>0.1</sub> In <sub>0.1</sub> Ga <sub>0.8</sub> N films using ultraviolet assisted photo-electrochemical etching route. <i>Journal of Alloys and Compounds</i> , <b>2015</b> , 649, 337-347	5.7	21
357	Quantitative analysis of morphological and photoluminescence properties of porous anodic alumina formed in sulfuric acid. <i>Journal of Porous Materials</i> , <b>2015</b> , 22, 1375-1382	2.4	6

356	Pt-decorated GaN nanowires with significant improvement in H <sub>2</sub> gas-sensing performance at room temperature. <i>Journal of Colloid and Interface Science</i> , <b>2015</b> , 460, 135-45	9.3	19
355	Growth behaviors of platinum-assisted GaN nanostructures in vapor-liquid-solid mechanism. <i>Materials Science in Semiconductor Processing</i> , <b>2015</b> , 39, 559-564	4.3	2
354	Ultrathin Wafer Pre-Assembly and Assembly Process Technologies: A Review. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>2015</b> , 40, 251-290	10.1	25
353	Microwave-assisted chemical bath deposition of nanocrystalline CdS thin films with superior photodetection characteristics. <i>Sensors and Actuators A: Physical</i> , <b>2015</b> , 230, 9-16	3.9	35
352	Growth and characterization of rutile TiO <sub>2</sub> nanorods on various substrates with fabricated fast-response metal-semiconductor-metal UV detector based on Si substrate. <i>Superlattices and Microstructures</i> , <b>2015</b> , 83, 549-564	2.8	21
351	Effect of deposition conditions on properties of nitrogen rich-InN nanostructures grown on anisotropic Si (110). <i>Materials Science in Semiconductor Processing</i> , <b>2015</b> , 35, 216-221	4.3	8
350	Growth of GaN on sputtered GaN buffer layer via low cost and simplified sol-gel spin coating method. <i>Vacuum</i> , <b>2015</b> , 119, 119-122	3.7	18
349	Effects of variations in precursor concentration on the growth of rutile TiO <sub>2</sub> nanorods on Si substrate with fabricated fast-response metal-semiconductor-metal UV detector. <i>Optical Materials</i> , <b>2015</b> , 44, 37-47	3.3	11
348	Effects of thermal treatment on the anodic growth of tungsten oxide films. <i>Thin Solid Films</i> , <b>2015</b> , 588, 44-49	2.2	20
347	Effect of QW thickness and numbers on performance characteristics of deep violet InGaN MQW lasers. <i>International Journal of Modern Physics B</i> , <b>2015</b> , 29, 1550081	1.1	3
346	Doping effects in p- and n-type layers of 390-nm InGaN DQW lasers. <i>International Journal of Modern Physics B</i> , <b>2015</b> , 29, 1550118	1.1	
345	Structural and optical characteristics of porous InAlGaIn prepared by photoelectrochemical etching. <i>Journal of Alloys and Compounds</i> , <b>2015</b> , 622, 565-571	5.7	9
344	Novel InGaIn mesoporous grown by PA-MBE. <i>Materials Science in Semiconductor Processing</i> , <b>2015</b> , 29, 102-105	4.3	1
343	AlN/GaN/AlN heterostructures grown on Si substrate by plasma-assisted MBE for MSM UV photodetector applications. <i>Materials Science in Semiconductor Processing</i> , <b>2015</b> , 29, 231-237	4.3	12
342	Role of pre-annealing treatment in improving the porosity of gallium nitride on cubic silicon (100) substrate. <i>Materials Science in Semiconductor Processing</i> , <b>2015</b> , 30, 330-334	4.3	2
341	Highly sensitive fast-response UV photodiode fabricated from rutile TiO <sub>2</sub> nanorod array on silicon substrate. <i>Sensors and Actuators A: Physical</i> , <b>2015</b> , 221, 15-21	3.9	57
340	Comparative study of porous anodic alumina: effects of aluminium deposition methods. <i>Materials Science and Technology</i> , <b>2015</b> , 31, 709-714	1.5	6
339	Characteristics of titanium dioxide nanostructures synthesized via electrochemical anodization at different applied voltages <b>2015</b> ,		1

338	Stability of the anodic growth porous tungsten oxide in different solutions <b>2015</b> ,		2
337	The effect of electron blocking layer on the performance of MQW oxide-confined intracavity-contacted InGaN-based vertical cavity surface emitting lasers. <i>Optik</i> , <b>2015</b> , 126, 1377-1380	2.5	0
336	INFLUENCE OF WAVEGUIDE LAYERS ON DEEP VIOLET InGaN DQW LASERS PERFORMANCE. <i>Surface Review and Letters</i> , <b>2015</b> , 22, 1550051	1.1	
335	The influence of quaternary electron blocking layer on the performance characteristics of intracavity-contacted oxide-confined InGaN-based vertical cavity surface emitting lasers. <i>International Journal of Modern Physics B</i> , <b>2015</b> , 29, 1550230	1.1	
334	Effect of Nanosecond Laser Dicing on the Mechanical Strength and Fracture Mechanism of Ultrathin Si Dies With Cu Stabilization Layer. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , <b>2015</b> , 5, 1885-1897	1.7	5
333	Formation of scandium nitride (ScN) layer on gallium arsenide (GaAs) substrate using a combined technique of e-beam evaporator and ammonia annealing treatment. <i>Applied Surface Science</i> , <b>2015</b> , 359, 589-592	6.7	3
332	An investigation of sol-gel spin coating growth of wurtzite GaN thin film on 6H-SiC substrate. <i>Journal of Crystal Growth</i> , <b>2015</b> , 413, 1-4	1.6	11
331	Preparation and characterization of ZnxCd1-xS ternary alloys micro/nanostructures grown by thermal evaporation. <i>Materials Research Express</i> , <b>2015</b> , 2, 016501	1.7	3
330	Ni/Ag Schottky contacts on Al <sub>0.11</sub> Ga <sub>0.89</sub> N grown on Si (1 1 1) substrate by plasma-assisted MBE. <i>Composite Interfaces</i> , <b>2015</b> , 22, 127-135	2.3	0
329	Luminescence evolution of porous GaN thin films prepared via UV-assisted electrochemical etching. <i>Journal of Luminescence</i> , <b>2015</b> , 159, 303-311	3.8	5
328	Synthesis of Nanocrystalline CdS Thin Films via Microwave-Assisted Chemical Bath Deposition for Highly Photosensitive and Rapid Response Photodetectors. <i>Journal of Nanoelectronics and Optoelectronics</i> , <b>2015</b> , 10, 783-789	1.3	6
327	Growth and characterization of silicon nanowires catalyzed by Zn metal via Pulsed Plasma-Enhanced Chemical Vapor Deposition. <i>Superlattices and Microstructures</i> , <b>2014</b> , 68, 90-100	2.8	12
326	A high-sensitivity, fast-response, rapid-recovery p-n heterojunction photodiode based on rutile TiO <sub>2</sub> nanorod array on p-Si(1 1 1). <i>Applied Surface Science</i> , <b>2014</b> , 305, 445-452	6.7	56
325	Formation of Tungsten Oxide Nanostructures Prepared in Hydrochloric Acid. <i>Journal of the Electrochemical Society</i> , <b>2014</b> , 161, D202-D206	3.9	2
324	Synthesis of wurtzite GaN thin film via spin coating method. <i>Materials Science in Semiconductor Processing</i> , <b>2014</b> , 17, 63-66	4.3	18
323	One-dimensional GaN nanostructures prepared via chemical vapor deposition: Substrate induced size and dimensionality. <i>Ceramics International</i> , <b>2014</b> , 40, 9563-9569	5.1	11
322	Room-temperature synthesis of nanocrystalline titanium dioxide via electrochemical anodization. <i>Materials Science in Semiconductor Processing</i> , <b>2014</b> , 26, 130-136	4.3	12
321	The influence of growth temperatures on the characteristics of GaN nanowires: The Raman study. <i>Physica B: Condensed Matter</i> , <b>2014</b> , 434, 101-105	2.8	4

320	Fabrication and characterization of nanocrystalline CdS thin film-based optical sensor grown via microwave-assisted chemical bath deposition. <i>Superlattices and Microstructures</i> , <b>2014</b> , 67, 8-16	2.8	37
319	Post-Annealing Effects on ITO Thin Films RF Sputtered at Different Thicknesses on Si and Glass. <i>Advanced Materials Research</i> , <b>2014</b> , 925, 411-415	0.5	2
318	Crystal orientation dependence of polarized infrared reflectance response of hexagonal sapphire crystal. <i>Optical Materials</i> , <b>2014</b> , 37, 773-779	3.3	7
317	Low fraction of hexagonal inclusions in thick and bulk cubic GaN layers. <i>Applied Surface Science</i> , <b>2014</b> , 317, 1010-1014	6.7	12
316	Structural and photoluminescence studies of rutile TiO <sub>2</sub> nanorods prepared by chemical bath deposition method on Si substrates at different pH values. <i>Measurement: Journal of the International Measurement Confederation</i> , <b>2014</b> , 56, 155-162	4.6	39
315	Fabrication of aluminum nitride heterostructures on Si (1 1 1) substrate by plasma-assisted MBE. <i>Composite Interfaces</i> , <b>2014</b> , 21, 723-735	2.3	2
314	Effects of nitridation durations on the synthesis of wurtzite GaN thin films by spin coating method. <i>Journal of Sol-Gel Science and Technology</i> , <b>2014</b> , 71, 329-332	2.3	5
313	Improvement of performance characteristics of deep violet InGaN DQW lasers using a strip DQW active region. <i>Optik</i> , <b>2014</b> , 125, 4911-4915	2.5	4
312	Comparison of the structural and optical properties of porous In <sub>0.08</sub> Ga <sub>0.92</sub> N thin films synthesized by electrochemical etching. <i>Journal of Solid State Chemistry</i> , <b>2014</b> , 212, 242-248	3.3	2
311	Solvothermal growth of single-crystal CdS nanowires. <i>Bulletin of Materials Science</i> , <b>2014</b> , 37, 337-345	1.7	9
310	Hydrogen gas sensing performance of GaN nanowires-based sensor at low operating temperature. <i>Sensors and Actuators B: Chemical</i> , <b>2014</b> , 204, 497-506	8.5	39
309	Optical properties of CdS micro/nanocrystalline structures prepared via a thermal evaporation method. <i>Materials Science in Semiconductor Processing</i> , <b>2014</b> , 26, 87-92	4.3	23
308	Structural, optical and electrical characterization of ITO, ITO/Ag and ITO/Ni transparent conductive electrodes. <i>Applied Surface Science</i> , <b>2014</b> , 288, 599-603	6.7	28
307	Effect of annealing temperature on IR-detectors based on InN nanostructures. <i>Vacuum</i> , <b>2014</b> , 106, 46-48	3.7	12
306	Structural and optical properties of In-doped ZnO thin films under wet annealing. <i>Materials Letters</i> , <b>2014</b> , 116, 396-398	3.3	14
305	Fabrication and characterization of metal-semiconductor-metal photodetector based on porous InGaN. <i>Materials Chemistry and Physics</i> , <b>2014</b> , 144, 86-91	4.4	4
304	Photoluminescence spectra of nitrogen-rich InN thin films grown on Si(110) and photoelectrochemical etched Si(110). <i>Vacuum</i> , <b>2014</b> , 101, 217-220	3.7	9
303	Structural characterizations of GaN nanowires grown on Si (111) substrates by thermal evaporation. <i>Materials Letters</i> , <b>2014</b> , 114, 140-143	3.3	4

302	Pseudo random number generator based on quantum chaotic map. <i>Communications in Nonlinear Science and Numerical Simulation</i> , <b>2014</b> , 19, 101-111	3.7	111
301	Ohmic-rectifying conversion of Ni contacts on ZnO and the possible determination of ZnO thin film surface polarity. <i>PLoS ONE</i> , <b>2014</b> , 9, e86544	3.7	7
300	Determination of acceptor concentration, depletion width, donor level movement and sensitivity factor of ZnO on diamond heterojunction under UV illumination. <i>PLoS ONE</i> , <b>2014</b> , 9, e89348	3.7	7
299	Effect of thermal annealing on GaN pn-junction diode with Pt/Ag as ohmic contact. <i>Composite Interfaces</i> , <b>2014</b> , 21, 371-380	2.3	1
298	Applications of the image processing method on the structure measurements in porous GaN. <i>Journal of Experimental Nanoscience</i> , <b>2014</b> , 9, 87-95	1.9	4
297	Synthesis, characterization, and effect of concentration variation on metal oxide nanostructures. <i>Composite Interfaces</i> , <b>2014</b> , 21, 217-232	2.3	1
296	Effects of Nitridation Temperatures on Gallium Nitride Thin Films Formed on Silicon Substrates. <i>Advanced Materials Research</i> , <b>2014</b> , 895, 57-62	0.5	
295	Fabrication Gallium Nitride (GaN) Nanowires by Thermal Chemical Vapor Deposition (TCVD) Technique. <i>Advanced Materials Research</i> , <b>2014</b> , 925, 450-454	0.5	3
294	Characterization Methods for Ultrathin Wafer and Die Quality: A Review. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , <b>2014</b> , 4, 2042-2057	1.7	19
293	Improved optoelectronics properties of ITO-based transparent conductive electrodes with the insertion of Ag/Ni under-layer. <i>Applied Surface Science</i> , <b>2014</b> , 315, 387-391	6.7	10
292	Growth of Rutile TiO <sub>2</sub> Nanorods by Chemical Bath Deposition Method on Silicon Substrate at Different Annealing Temperature. <i>Applied Mechanics and Materials</i> , <b>2014</b> , 624, 129-133	0.3	5
291	Improvement of Porous GaAs (100) Structure through Electrochemical Etching Based on DMF Solution. <i>Journal of Nanomaterials</i> , <b>2014</b> , 2014, 1-7	3.2	5
290	Fabrication of porous aluminium nitride films on silicon substrate for a better overgrown layer. <i>Materials Research Innovations</i> , <b>2014</b> , 18, S6-375-S6-377	1.9	1
289	Surface phonon polariton responses of hexagonal sapphire crystals with non-polar and semi-polar crystallographic planes. <i>Optics Letters</i> , <b>2014</b> , 39, 5467-70	3	4
288	Formation and Optical Studies of Porous GaN Thin Films via UV-Assisted Electrochemical Etching Approach. <i>Advanced Materials Research</i> , <b>2014</b> , 895, 45-50	0.5	1
287	Electrical Characterization of Al/Ag Contacts on Al-Zn Codoped SnO <sub>2</sub> Thin Films Deposited by Solid-State Chemical Vapor Deposition. <i>Advanced Materials Research</i> , <b>2014</b> , 925, 433-435	0.5	
286	Nanoporous InGaN prepared by KOH electrochemical etching with different light sources. <i>Microelectronic Engineering</i> , <b>2014</b> , 126, 107-112	2.5	5
285	Effect of Reagents Molar Concentration on CdS Thin Films Properties Grown by Chemical Bath Deposition under Microwave Irradiation. <i>Advanced Materials Research</i> , <b>2014</b> , 925, 263-267	0.5	

284	Characteristics of Cuprous Oxide Thin Films Deposited on Glass and Polyethylene Terephthalate Substrates. <i>Advanced Materials Research</i> , <b>2014</b> , 895, 29-34	0.5	
283	Nanocoral PbS Films Schottky Solar Cell. <i>Advanced Materials Research</i> , <b>2014</b> , 925, 605-609	0.5	3
282	Characteristics of porous GaN prepared by KOH photoelectrochemical etching. <i>Materials Research Innovations</i> , <b>2014</b> , 18, S6-412-S6-416	1.9	3
281	Porous GaN for Gas Sensing Application. <i>Advanced Materials Research</i> , <b>2014</b> , 1043, 50-56	0.5	2
280	Characterization of ITO/Ag and ITO/Ni Bi-Layer Transparent Conductive Electrodes. <i>Advanced Materials Research</i> , <b>2014</b> , 1024, 75-78	0.5	0
279	Properties of Pt Schottky Contact on Porous In <sub>0.27</sub> Ga <sub>0.73</sub> N Thin Film Revealed from I-V Measurements. <i>Advanced Materials Research</i> , <b>2014</b> , 895, 558-563	0.5	
278	Electrochemical Self-Assembly of ZnO Nanosheetlike Structures. <i>Applied Mechanics and Materials</i> , <b>2014</b> , 606, 3-7	0.3	
277	Calculation of dispersion of surface and interface phonon polariton resonances in wurtzite semiconductor multilayer system taking damping effects into account. <i>Thin Solid Films</i> , <b>2014</b> , 551, 114-119	2.2	5
276	Polarized infrared reflectance study of free standing cubic GaN grown by molecular beam epitaxy. <i>Materials Chemistry and Physics</i> , <b>2014</b> , 146, 121-128	4.4	4
275	Characteristics of MSM photodetector fabricated on porous In <sub>0.08</sub> Ga <sub>0.92</sub> N. <i>Measurement: Journal of the International Measurement Confederation</i> , <b>2014</b> , 50, 172-174	4.6	14
274	Controlled porosity of GaN using different pore size of Si (100) substrates. <i>Superlattices and Microstructures</i> , <b>2014</b> , 73, 54-59	2.8	5
273	Temperature-dependent current conduction mechanism and charge trapping in Ta <sub>2</sub> O <sub>5</sub> RF-sputtered on GaN. <i>Current Applied Physics</i> , <b>2014</b> , 14, 23-29	2.6	8
272	Performance characteristics of deep violet InGaN DQW laser diodes with InGaN/GaN superlattice waveguide layers. <i>Optik</i> , <b>2014</b> , 125, 341-344	2.5	9
271	Characterization of surface roughness of Pt Schottky contacts on quaternary n-Al <sub>0.08</sub> In <sub>0.08</sub> Ga <sub>0.84</sub> N thin film assessed by atomic force microscopy and fractal analysis. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2014</b> , 25, 466-477	2.1	32
270	One-step growth of curled GaN nanowires using chemical vapor deposition method. <i>Vacuum</i> , <b>2013</b> , 95, 6-11	3.7	4
269	Porous WO <sub>3</sub> formed by anodization in oxalic acid. <i>Journal of Porous Materials</i> , <b>2013</b> , 20, 997-1002	2.4	16
268	Preparation and characterization of silicon nanowires catalyzed by aluminum. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2013</b> , 48, 21-28	3	6
267	InGaN-based multi-quantum well light-emitting diode structure with the insertion of superlattices under-layer. <i>Superlattices and Microstructures</i> , <b>2013</b> , 60, 201-207	2.8	2



266	MBE growth of GaN pn-junction photodetector on AlN/Si(1 1 1) substrate with Ni/Ag as ohmic contact. <i>Superlattices and Microstructures</i> , <b>2013</b> , 56, 35-44	2.8	22
265	Structural and optical properties of Au-catalyzed SiNWs grown using pulsed plasma-enhanced chemical vapour deposition. <i>Superlattices and Microstructures</i> , <b>2013</b> , 61, 134-145	2.8	12
264	Effects of traps and polarization charges on device performance of AlGaIn/GaN high electron mobility transistors. <i>Superlattices and Microstructures</i> , <b>2013</b> , 63, 141-148	2.8	5
263	Numerical study of performance characteristics of deep violet InGaIn DQW laser diodes with AlInGaIn quaternary multi quantum barrier electron blocking layer. <i>Optik</i> , <b>2013</b> , 124, 6765-6768	2.5	11
262	Nanoporous InGaIn of high In composition prepared by KOH electrochemical etching. <i>Materials Science in Semiconductor Processing</i> , <b>2013</b> , 16, 2051-2057	4.3	11
261	Effects of annealing on the optical and electrical properties of CdO thin films prepared by thermal evaporation. <i>Materials Letters</i> , <b>2013</b> , 105, 84-86	3.3	18
260	Effects of oxygen percentage on the growth of copper oxide thin films by reactive radio frequency sputtering. <i>Materials Chemistry and Physics</i> , <b>2013</b> , 140, 243-248	4.4	40
259	Fabrication of ZnO nanorod/p-GaN high-brightness UV LED by microwave-assisted chemical bath deposition with Zn(OH) <sub>2</sub> /BVA nanocomposites as seed layer. <i>Optical Materials</i> , <b>2013</b> , 35, 1035-1041	3.3	23
258	X-ray analysis of nanoporous TiO <sub>2</sub> synthesized by electrochemical anodization. <i>Superlattices and Microstructures</i> , <b>2013</b> , 64, 37-43	2.8	10
257	Study on effect of quantum well number on performance characteristics of GaN-based vertical cavity surface emitting laser. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2013</b> , 50, 61-66	3	3
256	High performance room temperature GaN-nanowires hydrogen gas sensor fabricated by chemical vapor deposition (CVD) technique. <i>International Journal of Hydrogen Energy</i> , <b>2013</b> , 38, 14085-14101	6.7	49
255	Growth and characterization of different structured CdO using a vapor transport. <i>Materials Letters</i> , <b>2013</b> , 102-103, 12-14	3.3	15
254	Infrared reflectance studies of hillock-like porous zinc oxide thin films. <i>Thin Solid Films</i> , <b>2013</b> , 539, 70-74	2.2	3
253	Effect of thermal annealing on ohmic contacts properties of undoped and Si-doped Al <sub>0.15</sub> Ga <sub>0.85</sub> N on Si(1 1 1) substrate grown by PA-MBE. <i>Optik</i> , <b>2013</b> , 124, 4257-4259	2.5	
252	Synthesis of two-dimensional gallium nitride via spin coating method: influences of nitridation temperatures. <i>Journal of Sol-Gel Science and Technology</i> , <b>2013</b> , 68, 95-101	2.3	16
251	Influence of deposition temperature on the growth of rutile TiO <sub>2</sub> nanostructures by CBD method on seed layer prepared by RF magnetron sputtering. <i>Superlattices and Microstructures</i> , <b>2013</b> , 64, 27-36	2.8	28
250	Growth and characterization of CdS single-crystalline micro-rod photodetector. <i>Superlattices and Microstructures</i> , <b>2013</b> , 54, 137-145	2.8	35
249	Room temperature hydrogen gas sensor based on ZnO nanorod arrays grown on a SiO <sub>2</sub> /Si substrate via a microwave-assisted chemical solution method. <i>Journal of Alloys and Compounds</i> , <b>2013</b> , 546, 107-111	5.7	73

248	A high-sensitivity room-temperature hydrogen gas sensor based on oblique and vertical ZnO nanorod arrays. <i>Sensors and Actuators B: Chemical</i> , <b>2013</b> , 176, 360-367	8.5	120
247	Influence of Al-flux on the growth of AlN/GaN/AlN films on Si (111) substrate by MBE. <i>Superlattices and Microstructures</i> , <b>2013</b> , 64, 367-374	2.8	3
246	Growth and conversion of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> nanobelts into GaN nanowires via catalyst-free chemical vapor deposition technique. <i>Superlattices and Microstructures</i> , <b>2013</b> , 54, 215-224	2.8	23
245	Synthesis of nanocrystalline In <sub>2</sub> O <sub>3</sub> on different Si substrates at wet oxidation environment. <i>Optik</i> , <b>2013</b> , 124, 2679-2681	2.5	3
244	Growth of self-assembled InGaN quantum dots on Si (111) at reduced temperature by molecular beam epitaxy. <i>Thin Solid Films</i> , <b>2013</b> , 544, 33-36	2.2	1
243	Fabrication of GaN nanowires on porous GaN substrate by thermal evaporation. <i>Materials Science in Semiconductor Processing</i> , <b>2013</b> , 16, 485-488	4.3	3
242	pn-Junction photodiode based on GaN grown on Si (111) by plasma-assisted molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , <b>2013</b> , 16, 1859-1864	4.3	10
241	A comparative study of the structural and electrical properties of n-type InGaN epilayer grown by MBE and commercially. <i>Superlattices and Microstructures</i> , <b>2013</b> , 60, 224-230	2.8	5
240	Structural properties of porous In <sub>0.08</sub> Ga <sub>0.92</sub> N synthesized using photoelectrochemical etching. <i>Materials Letters</i> , <b>2013</b> , 107, 367-369	3.3	6
239	Substrate surface polariton splitting due to thin zinc oxide and aluminum nitride films presence. <i>Applied Surface Science</i> , <b>2013</b> , 267, 93-96	6.7	4
238	Study of growth mechanism of self-catalytic branched GaN nanowires. <i>Superlattices and Microstructures</i> , <b>2013</b> , 58, 38-43	2.8	1
237	Surface and optical phonon characteristics of ZnO/diamond heterostructure. <i>Ceramics International</i> , <b>2013</b> , 39, S529-S532	5.1	0
236	PbS nanocrystal solar cells fabricated using microwave-assisted chemical bath deposition. <i>International Journal of Hydrogen Energy</i> , <b>2013</b> , 38, 807-815	6.7	29
235	Structural and optical properties of nanocrystalline lead sulfide thin films prepared by microwave-assisted chemical bath deposition. <i>Materials Science in Semiconductor Processing</i> , <b>2013</b> , 16, 971-979	4.3	20
234	Fabrication and characterisations of n-CdS/p-PbS heterojunction solar cells using microwave-assisted chemical bath deposition. <i>Solar Energy</i> , <b>2013</b> , 89, 143-151	6.8	50
233	Fast UV detection and hydrogen sensing by ZnO nanorod arrays grown on a flexible Kapton tape. <i>Materials Science-Poland</i> , <b>2013</b> , 31, 180-185	0.6	15
232	Optical and structural properties of porous zinc oxide fabricated via electrochemical etching method. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2013</b> , 178, 956-959	3.1	5
231	Sensing devices based on ZnO hexagonal tube-like nanostructures grown on p-GaN heterojunction by wet thermal evaporation. <i>Thin Solid Films</i> , <b>2013</b> , 540, 212-220	2.2	15

230	Fabrication of porous ZnO via electrochemical etching using 10 wt% potassium hydroxide solution. <i>Materials Science in Semiconductor Processing</i> , <b>2013</b> , 16, 70-76	4.3	7
229	Fabrication and characterization of ZnO nanorods/p-6H-SiC heterojunction LED by microwave-assisted chemical bath deposition. <i>Superlattices and Microstructures</i> , <b>2013</b> , 53, 31-38	2.8	39
228	Plasma-assisted MBE growth of AlN/GaN/AlN heterostructures on Si (1 1 1) substrate. <i>Superlattices and Microstructures</i> , <b>2013</b> , 60, 500-507	2.8	11
227	Light Extraction from GaN-Microcavity. <i>Nano Hybrids</i> , <b>2013</b> , 3, 51-65		
226	Polarized infrared reflectance characterization of wurtzite ZnO/GaN heterostructure on 6H-SiC substrate <b>2013</b> ,		1
225	Comparative study on structural and optical properties of nitrogen rich InN on Si(110) and 6H-SiC. <i>Surface Engineering</i> , <b>2013</b> , 29, 561-565	2.6	10
224	Growth of InN thin films on different Si substrates at ambient temperature. <i>Microelectronics International</i> , <b>2013</b> , 30, 63-67	0.8	7
223	Growth of Vertically Aligned ZnO Nanorods Arrays by Hydrothermal Method. <i>Advanced Materials Research</i> , <b>2013</b> , 795, 616-619	0.5	4
222	Fabrication of InN based photodetector using porous silicon buffer layer. <i>Surface Engineering</i> , <b>2013</b> , 29, 772-777	2.6	15
221	Free Catalyst Synthesis of GaN Nanostructures on Si-Substrate via CVD. <i>Materials Science Forum</i> , <b>2013</b> , 756, 59-65	0.4	
220	Microstructural and Optical Properties of SnO Thin Film by Thermal Evaporation. <i>Advanced Materials Research</i> , <b>2013</b> , 795, 558-562	0.5	1
219	Ultraviolet Photoresponse Properties of Zinc Oxide Nanorods on Heavily Boron-Doped Diamond Heterostructure. <i>Advanced Materials Research</i> , <b>2013</b> , 832, 172-177	0.5	1
218	A Study of Properties of the Nanocrystalline CdO Thin Film Prepared by Solid-Vapor Deposition Method. <i>Materials Science Forum</i> , <b>2013</b> , 756, 54-58	0.4	3
217	STRUCTURE AND OPTICAL PROPERTIES OF InN THIN FILM GROWN ON SiC BY REACTIVE RF MAGNETRON SPUTTERING. <i>Surface Review and Letters</i> , <b>2013</b> , 20, 1350008	1.1	8
216	Surface phonon polariton characteristic of honeycomb nanoporous GaN thin films. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 101601	3.4	16
215	Photoelectrochemical Fabrication of Porous GaN and Their Applications in Ultraviolet and Ammonia Sensing. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JK03	1.4	7
214	THE STUDY OF Al <sub>0.29</sub> Ga <sub>0.71</sub> N-BASED SCHOTTKY PHOTODIODES GROWN ON SILICON BY PLASMA-ASSISTED MOLECULAR BEAM EPITAXY. <i>Modern Physics Letters B</i> , <b>2013</b> , 27, 1350085	1.6	
213	Improvement of the performance characteristics of deep violet InGaN multi-quantum-well laser diodes using step-graded electron blocking layers and a delta barrier. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 123108	2.5	17

212	The effects of quantum wells number and the built-in polarization on the performance of quaternary AlInGaN UV laser diode. <i>Optik</i> , <b>2012</b> , 123, 856-859	2.5	3
211	Nano and micro porous GaN characterization using image processing method. <i>Optik</i> , <b>2012</b> , 123, 1074-1078	12	
210	Surface phonon polariton of wurtzite AlN thin film grown on sapphire. <i>Materials Chemistry and Physics</i> , <b>2012</b> , 134, 493-498	4.4	5
209	Nanocrystalline ZnO film grown on porous silicon layer by radio frequency sputtering system. <i>Materials Letters</i> , <b>2012</b> , 68, 51-53	3.3	19
208	Simulation and optimization of deep violet InGaN double quantum well laser. <i>Optics Communications</i> , <b>2012</b> , 285, 746-750	2	12
207	Effective conversion efficiency enhancement of solar cell using ZnO/PS antireflection coating layers. <i>Solar Energy</i> , <b>2012</b> , 86, 541-547	6.8	61
206	Quaternary n-Al <sub>0.08</sub> In <sub>0.08</sub> Ga <sub>0.84</sub> N/p-Si-based solar cell. <i>Superlattices and Microstructures</i> , <b>2012</b> , 51, 480-485	7	
205	Structural and optical properties of nanocrystalline CdS thin films prepared using microwave-assisted chemical bath deposition. <i>Thin Solid Films</i> , <b>2012</b> , 520, 3477-3484	2.2	83
204	The effect of oxide aperture diameter on the electrical characteristics of the GaN-based vertical cavity surface emitting laser. <i>IEICE Electronics Express</i> , <b>2012</b> , 9, 179-184	0.5	
203	Optical properties of photo-electrochemical etching of anisotropic silicon (110). <i>IEICE Electronics Express</i> , <b>2012</b> , 9, 752-757	0.5	6
202	Room-temperature hydrogen gas sensor with ZnO nanorod arrays grown on a quartz substrate. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2012</b> , 46, 254-258	3	12
201	Characterization of GaN nanowires grown on PSi, PZnO and PGaN on Si (111) substrates by thermal evaporation <b>2012</b> ,		1
200	Growth and characterization of ZnxCd <sub>1-x</sub> S nanoflowers by microwave-assisted chemical bath deposition. <i>Journal of Alloys and Compounds</i> , <b>2012</b> , 541, 227-233	5.7	34
199	Effects of applied voltage on the properties of anodic zirconia thin film on (100) silicon. <i>Thin Solid Films</i> , <b>2012</b> , 522, 117-124	2.2	4
198	Defects in GaN film grown on Si (100) substrate <b>2012</b> ,		1
197	To develop porous Si as substrate for better quality GaN layer <b>2012</b> ,		3
196	Effects of Cavity Length on Optical Characteristics of Deep Violet InGaN DQW Lasers. <i>Advanced Materials Research</i> , <b>2012</b> , 626, 605-609	0.5	0
195	Structural and Optical Properties of In <sub>0.27</sub> Ga <sub>0.73</sub> N/Si (111) Film Grown Using PA-MBE Technique. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 368-372	0.5	3

194	Current-Voltage Characteristics of n-Al <sub>0.08</sub> In <sub>0.08</sub> Ga <sub>0.84</sub> N Schottky Diode Using Pt Metal Contact. <i>Advanced Materials Research</i> , <b>2012</b> , 501, 226-230	0.5	1
193	Synthesis and characterization of single-crystal CdS nanosheet for high-speed photodetection. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2012</b> , 44, 1716-1721	3	62
192	ZnO nanostructures grown on porous silicon substrate without catalyst <b>2012</b> ,		1
191	Microwave assisted chemical bath deposition of vertically aligned ZnO nanorods on a variety of substrates seeded by PVA/n(OH) <sub>2</sub> nanocomposites. <i>Applied Surface Science</i> , <b>2012</b> , 258, 4467-4472	6.7	23
190	Growth and analysis of GaN nanowire on PZnO by different-gas flow. <i>Applied Surface Science</i> , <b>2012</b> , 258, 6590-6594	6.7	7
189	Growth of CdS nanosheets and nanowires through the solvothermal method. <i>Journal of Crystal Growth</i> , <b>2012</b> , 359, 43-48	1.6	38
188	High-quality GaN nanowires grown on Si and porous silicon by thermal evaporation. <i>Applied Surface Science</i> , <b>2012</b> , 263, 50-53	6.7	8
187	An image encryption scheme based on quantum logistic map. <i>Communications in Nonlinear Science and Numerical Simulation</i> , <b>2012</b> , 17, 4653-4661	3.7	126
186	Preparation of chemically deposited thin films of CdS/PbS solar cell. <i>Superlattices and Microstructures</i> , <b>2012</b> , 52, 816-823	2.8	30
185	Fabrication and characterization of nanocrystalline n-CdO/p-Si as a solar cell. <i>Superlattices and Microstructures</i> , <b>2012</b> , 52, 800-806	2.8	20
184	Characterization of nanocrystalline PbS thin films prepared using microwave-assisted chemical bath deposition. <i>Materials Science in Semiconductor Processing</i> , <b>2012</b> , 15, 564-571	4.3	38
183	Porous silicon based violet-UV detector <b>2012</b> ,		2
182	EFFECT OF CURRENT DENSITY ON OPTICAL PROPERTIES OF ANISOTROPIC PHOTOELECTROCHEMICAL ETCHED SILICON (110). <i>Modern Physics Letters B</i> , <b>2012</b> , 26, 1250131	1.6	4
181	Analytical and visual modeling of InGaN/GaN single quantum well laser based on rate equations. <i>Optics and Laser Technology</i> , <b>2012</b> , 44, 12-20	4.2	16
180	Morphological, optical, and Raman characteristics of ZnO nanoflakes prepared via a sol-gel method. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 143-147	1.6	46
179	Surface phonon polariton characteristics of wurtzite ZnO thin film grown on silicon substrate. <i>Physica Status Solidi (B): Basic Research</i> , <b>2012</b> , 249, 1058-1062	1.3	2
178	Growth of Nanocrystalline PbS Thin Films by Solid-Vapor Deposition. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 1-6	0.5	2
177	Growth of ZnO Nanostructures at Different Temperatures without Catalyst by Wet Thermal Oxidation Process. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 132-136	0.5	1

176	Gan Nanowire Growth by Thermal Evaporation Method. <i>Advanced Materials Research</i> , <b>2012</b> , 501, 276-280.	0.5	
175	Fabrication and Structural and Optical Characterizations of GaN Nano and Micro Structures Grown by Thermal Evaporation Method. <i>Advanced Materials Research</i> , <b>2012</b> , 545, 88-92	0.5	
174	Structural and Optical Properties of Nanocrystalline CdO Thin Film Growth by Solid-Vapor Deposition. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 241-245	0.5	2
173	Nanoporous ZnO prepared by electrochemical anodization deposition <b>2012</b> ,		2
172	Electrical and Optical Characterization of Mg Doping in GaN. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 453-457	0.5	
171	A Simple Method to Prepare Indium Oxide Nanoparticles on Si (110). <i>Advanced Materials Research</i> , <b>2012</b> , 620, 193-197	0.5	1
170	Comparative study of ultraviolet detectors based on ZnO nanostructures grown on different substrates. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 074510	2.5	30
169	High sensitivity and fast response and recovery times in a ZnO nanorod array/p-Si self-powered ultraviolet detector. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 261108	3.4	84
168	Electrochemical Impregnation of Silver Nanostructures in Titanium Dioxide Nanotubes. <i>Journal of the Electrochemical Society</i> , <b>2012</b> , 159, D742-D746	3.9	2
167	GaN ON SILICON SUBSTRATE WITH AlN BUFFER LAYER FOR UV PHOTODIODE. <i>Journal of Nonlinear Optical Physics and Materials</i> , <b>2012</b> , 21, 1250014	0.8	4
166	InN PHOTOCONDUCTORS ON DIFFERENT ORIENTATIONS OF Si SUBSTRATES. <i>International Journal of Modern Physics B</i> , <b>2012</b> , 26, 1250137	1.1	8
165	Reactive Sputtering Growth and Characterizations of InN Thin Films on Si Substrates. <i>Advanced Materials Research</i> , <b>2012</b> , 545, 290-293	0.5	
164	Compositional and Structural Characterization of Heterostructure InGaN-Based Light-Emitting Diode by High Resolution X-Ray Diffraction. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 22-27	0.5	4
163	Structural and Surface Studies of Undoped Porous GaN Grown on Sapphire. <i>Advanced Materials Research</i> , <b>2012</b> , 620, 45-49	0.5	1
162	Fabrication of porous ZnO thin films using wet chemical etching with 0.5% HNO <sub>3</sub> . <i>Microelectronics International</i> , <b>2012</b> , 29, 96-100	0.8	2
161	Performance enhancement of deep violet indium gallium nitride double quantum well lasers using delta barrier close to electron blocking layer. <i>Journal of Nanophotonics</i> , <b>2012</b> , 6, 063514	1.1	12
160	Surface and interface phonon polariton characteristics of wurtzite ZnO/GaN heterostructure. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 241909	3.4	6
159	Enhanced Properties of Porous GaN Prepared by UV Assisted Electrochemical Etching. <i>Advanced Materials Research</i> , <b>2011</b> , 364, 90-94	0.5	1

158	The influence of Ga source and substrate position on the growth of low dimensional GaN wires by chemical vapour deposition. <i>Applied Surface Science</i> , <b>2011</b> , 257, 10052-10055	6.7	7
157	The influence of growth temperatures on the characteristics of GaN nanowires. <i>Applied Surface Science</i> , <b>2011</b> , 258, 542-546	6.7	8
156	Enhancing photoresponse time of low cost Pd/ZnO nanorods prepared by thermal evaporation techniques for UV detection. <i>Applied Surface Science</i> , <b>2011</b> , 258, 461-465	6.7	18
155	Quaternary ultraviolet AlInGaN MQW laser diode performance using quaternary AlInGaN electron blocking layer. <i>Optics Express</i> , <b>2011</b> , 19, 9245-54	3.3	29
154	ZnO nanocoral reef grown on porous silicon substrates without catalyst. <i>Journal of Alloys and Compounds</i> , <b>2011</b> , 509, 5627-5630	5.7	35
153	High-quality vertically aligned ZnO nanorods synthesized by microwave-assisted CBD with ZnOBVA complex seed layer on Si substrates. <i>Journal of Alloys and Compounds</i> , <b>2011</b> , 509, 6711-6719	5.7	77
152	Far Infrared Optical Properties of Bulk Wurtzite Zinc Oxide Semiconductor. <i>Journal of Materials Science and Technology</i> , <b>2011</b> , 27, 465-470	9.1	10
151	Improved performance of a crystalline silicon solar cell based on ZnO/PS anti-reflection coating layers. <i>Superlattices and Microstructures</i> , <b>2011</b> , 50, 517-528	2.8	15
150	The effect of etching time of porous silicon on solar cell performance. <i>Superlattices and Microstructures</i> , <b>2011</b> , 50, 647-658	2.8	48
149	Polarized infrared reflectance studies for wurtzite InN epilayers on Si(111) grown by molecular beam epitaxy. <i>Thin Solid Films</i> , <b>2011</b> , 520, 739-742	2.2	5
148	The growth of heavily Mg-doped GaN thin film on Si substrate by molecular beam epitaxy. <i>Thin Solid Films</i> , <b>2011</b> , 520, 756-760	2.2	12
147	The effects of morphological changes on the vibrational properties of self-organized TiO <sub>2</sub> nanotubes. <i>Thin Solid Films</i> , <b>2011</b> , 520, 807-812	2.2	6
146	Nanostructured GaN on silicon fabricated by electrochemical and laser-induced etching. <i>Materials Letters</i> , <b>2011</b> , 65, 61-63	3.3	7
145	Effect of Postdeposition Annealing in Oxygen Ambient on Gallium-Nitride-Based MOS Capacitors With Cerium Oxide Gate. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 122-131	2.9	27
144	Improved performance of solar cell based on porous silicon surfaces. <i>Optik</i> , <b>2011</b> , 122, 2075-2077	2.5	21
143	Investigation of forming-gas annealed CeO <sub>2</sub> thin film on GaN. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2011</b> , 22, 583-591	2.1	24
142	Porous silicon nanowires fabricated by electrochemical and laser-induced etching. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2011</b> , 22, 717-723	2.1	20
141	The effect of sub-band gap photon illumination on the properties of GaN layers grown on Si(111) by MBE. <i>Journal of Nanoparticle Research</i> , <b>2011</b> , 13, 7139-7148	2.3	6

140	Laser-induced etching parameters impact on optical properties of the silicon nanostructures. <i>Science China Technological Sciences</i> , <b>2011</b> , 54, 58-62	3.5	8
139	A study of the operating parameters and barrier thickness of Al <sub>0.08</sub> In <sub>0.08</sub> Ga <sub>0.84</sub> N/Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N double quantum well laser diodes. <i>Science China Technological Sciences</i> , <b>2011</b> , 54, 47-51	3.5	6
138	Effect of postdeposition annealing on electrical properties of RF-magnetron sputtered CeO <sub>x</sub> gate on 4H-silicon carbide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2011</b> , 208, 1925-1930	1.6	2
137	Photoluminescence and XRD Crystalline Studies of In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N Quaternary Alloys. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2011</b> , 17, 012006	0.4	1
136	Photoluminescence, raman and X-ray diffraction studies of porous GaN grown on sapphire <b>2011</b> ,		1
135	Synthesis of Porous Ni-Doped SnO <sub>2</sub> Thin Film by Using Spray Pyrolysis. <i>Composite Interfaces</i> , <b>2011</b> , 18, 371-376	2.3	4
134	Effect of Al mole fraction on structural and electrical properties of Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures grown by plasma-assisted molecular beam epitaxy. <i>Applied Surface Science</i> , <b>2011</b> , 257, 4159-4164	6.7	18
133	Fabrication of titanium dioxide nanofibers via anodic oxidation. <i>Applied Surface Science</i> , <b>2011</b> , 257, 4706-4708	4.7	5
132	New optical features to enhance solar cell performance based on porous silicon surfaces. <i>Applied Surface Science</i> , <b>2011</b> , 257, 6112-6117	6.7	62
131	Structural, optical and electrical properties of undoped and Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> N thin films on Si (111) substrate grown by PA-MBE. <i>Physica B: Condensed Matter</i> , <b>2011</b> , 406, 1267-1271	2.8	4
130	The effect of anti-reflection coating of porous silicon on solar cells efficiency. <i>Optik</i> , <b>2011</b> , 122, 1462-1465	6.5	33
129	Effect of post-deposition annealing temperature on CeO <sub>2</sub> thin film deposited on silicon substrate via RF magnetron sputtering technique. <i>Materials Science in Semiconductor Processing</i> , <b>2011</b> , 14, 101-107	4.3	12
128	Characterization of Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N quaternary alloys grown on sapphire substrates by molecular-beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , <b>2011</b> , 14, 164-169	4.3	3
127	Surface phonon polariton characteristics of bulk wurtzite ZnO crystal. <i>Physica B: Condensed Matter</i> , <b>2011</b> , 406, 115-118	2.8	6
126	Experimental investigation of long-wavelength optical lattice vibrations in quaternary Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N alloys and comparison with results from the pseudo-unit cell model. <i>Physica B: Condensed Matter</i> , <b>2011</b> , 406, 1379-1384	2.8	5
125	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO <sub>2</sub> ) gate deposited on GaN and SiC substrates. <i>Journal of Crystal Growth</i> , <b>2011</b> , 326, 2-8	1.6	33
124	Porous GaN on Si(111) and its application to hydrogen gas sensor. <i>Sensors and Actuators B: Chemical</i> , <b>2011</b> , 155, 699-708	8.5	40
123	Stiffness properties of porous silicon nanowires fabricated by electrochemical and laser-induced etching. <i>Superlattices and Microstructures</i> , <b>2011</b> , 50, 119-127	2.8	16



122	Studies of surface and interface phonon polariton characteristics of wurtzite ZnO thin film on wurtzite 6H-SiC substrate by p-polarized infrared attenuated total reflection spectroscopy. <i>Thin Solid Films</i> , <b>2011</b> , 519, 3703-3708	2.2	12
121	Theoretical studies of surface phonon polariton in wurtzite AlInN ternary alloy. <i>Thin Solid Films</i> , <b>2011</b> , 519, 5481-5485	2.2	6
120	Strong Room Temperature 505 nm Emission from Hexagonal Crack Free InGaN Thin Film on Si(111) Grown by MBE. <i>Composite Interfaces</i> , <b>2011</b> , 18, 37-47	2.3	1
119	Characterization of GaN p-n Junction Grown on Si (111) Substrate by Plasma-Assisted Molecular Beam Epitaxy. <i>Advanced Materials Research</i> , <b>2011</b> , 364, 139-143	0.5	
118	The Fabrication of Ag Islands on AlN/GaN/AlN/Si(111) by Using Thermal Evaporator and Thermal Annealing Methods. <i>Advanced Materials Research</i> , <b>2011</b> , 364, 327-332	0.5	1
117	Structural Properties of Nanocrystalline PbS Thin Films Prepared by Chemical Bath Deposition Method. <i>Advanced Materials Research</i> , <b>2011</b> , 364, 60-64	0.5	8
116	Dispersion of Surface and Interface Phonon Polariton Modes in Wurtzite Based Multilayer System. <i>Journal of the Physical Society of Japan</i> , <b>2011</b> , 80, 084712	1.5	9
115	Optical and Structural Characterizations of GaN Nanostructures. <i>Advanced Materials Research</i> , <b>2011</b> , 364, 348-352	0.5	5
114	The Investigation of Porous Al <sub>x</sub> Ga <sub>1-x</sub> N Layers on Si (111) Substrate with GaN/AlN as Buffer Layer. <i>Advanced Materials Research</i> , <b>2011</b> , 364, 164-168	0.5	
113	Optical Analysis of Nanocrystalline ZnO Films Coated on Porous Silicon by Radio Frequency (RF) Magnetron Sputtering. <i>Composite Interfaces</i> , <b>2011</b> , 18, 441-448	2.3	7
112	Catalyst-free growth and characterization of ZnO nanoscrewdrivers prepared by thermal evaporation. <i>Microelectronics International</i> , <b>2011</b> , 28, 3-6	0.8	2
111	A Study on the Effect of Process Parameters on Surface Topography of Al Thin Films on Various Substrates Using AFM. <i>Advanced Materials Research</i> , <b>2011</b> , 383-390, 903-908	0.5	
110	Study of electrical characteristics of ZnO Schottky photodiode on Si substrate. <i>Microelectronics International</i> , <b>2011</b> , 28, 8-11	0.8	4
109	X-ray diffraction studies of Al <sub>x</sub> Ga <sub>1-x</sub> N (0001) ternary alloys grown on sapphire substrate. <i>Microelectronics International</i> , <b>2011</b> , 28, 44-48	0.8	0
108	FORTHCOMING GALLIUM NITRIDE BASED POWER DEVICES IN PROMPTING THE DEVELOPMENT OF HIGH POWER APPLICATIONS. <i>Modern Physics Letters B</i> , <b>2011</b> , 25, 77-88	1.6	6
107	Effects of N <sub>2</sub> O Postdeposition Annealing on Metal-Organic Decomposed CeO <sub>2</sub> Gate Oxide Spin-Coated on GaN Substrate. <i>Journal of the Electrochemical Society</i> , <b>2011</b> , 158, H423	3.9	21
106	Synthesis of ZnO Nanosheets by a Combined Electrodeposition and Illumination Method. <i>Composite Interfaces</i> , <b>2011</b> , 18, 543-550	2.3	3
105	Nanocrystalline ZnO Film Grown on Porous SnO <sub>2</sub> /Si(111) Substrate. <i>Composite Interfaces</i> , <b>2011</b> , 18, 627-632		2

104	Tetrapod-Like ZnO Nanostructures Deposited on Si Substrates with AlN as Buffer Layer. <i>Composite Interfaces</i> , <b>2011</b> , 18, 49-56	2.3	2
103	Single Crystalline ZnO Nanowires by Oxidizing Granular Zinc Film. <i>Journal of Dispersion Science and Technology</i> , <b>2011</b> , 32, 677-679	1.5	
102	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. <i>Journal of Nanomaterials</i> , <b>2011</b> , 2011, 1-7	3.2	21
101	Effect of Porosity on the Characteristics of GaN Grown on Sapphire <b>2011</b> ,		3
100	Growth and Characterization of High-Quality GaN Nanowires on PZnO and PGaN by Thermal Evaporation. <i>Journal of Nanomaterials</i> , <b>2011</b> , 2011, 1-6	3.2	2
99	Structural Properties Studies of GaN on 6H-SiC by Means of X-Ray Diffraction Technique. <i>Advanced Materials Research</i> , <b>2010</b> , 173, 40-43	0.5	
98	Porous Silicon as an Intermediate Buffer Layer for Zinc Oxide Nanorods. <i>Composite Interfaces</i> , <b>2010</b> , 17, 733-742	2.3	11
97	Effects of Postdeposition Annealing in Argon Ambient on Metallorganic Decomposed CeO <sub>2</sub> Gate Spin Coated on Silicon. <i>Journal of the Electrochemical Society</i> , <b>2010</b> , 157, H6	3.9	52
96	The Effects of Thermal Treatments on Microstructure Phosphorus-Doped ZnO Layers Grown by Thermal Evaporation. <i>Composite Interfaces</i> , <b>2010</b> , 17, 863-872	2.3	4
95	PSEUDO RANDOM NUMBER GENERATOR BASED ON SYNCHRONIZED CHAOTIC MAPS. <i>International Journal of Modern Physics C</i> , <b>2010</b> , 21, 275-290	1.1	7
94	RED LIGHT EMITTING SCHOTTKY DIODES ON p-TYPE GaN/AlN/Si(111) SUBSTRATE. <i>International Journal of Modern Physics B</i> , <b>2010</b> , 24, 1129-1135	1.1	2
93	MOS Characteristics of Metallorganic-Decomposed CeO <sub>2</sub> Spin-Coated on GaN. <i>Electrochemical and Solid-State Letters</i> , <b>2010</b> , 13, H116		19
92	CURRENT CONDUCTION MECHANISMS OF ATOMIC-LAYER-DEPOSITED Al <sub>2</sub> O <sub>3</sub> /NITRIDED SiO <sub>2</sub> STACKING GATE OXIDE ON 4H-SiC. <i>International Journal of Modern Physics B</i> , <b>2010</b> , 24, 5371-5378	1.1	1
91	THE STUDIES OF THERMAL ANNEALING ON Pt/AlGa <sub>n</sub> GROWN ON Si(111) BY PLASMA-ASSISTED MOLECULAR BEAM EPITAXY (PA-MBE). <i>Modern Physics Letters B</i> , <b>2010</b> , 24, 2889-2898	1.6	1
90	STRUCTURAL AND OPTICAL PROPERTIES OF ZnO SYNTHESIZED BY TEMPERATURE GRADIENT THERMAL OXIDATION. <i>Surface Review and Letters</i> , <b>2010</b> , 17, 497-503	1.1	2
89	The Influence of Geometrical Structure of AlInGa <sub>n</sub> Double Quantum Well (DQWs) UV Diode Laser on Its Performance and Operating Parameters <b>2010</b> ,		1
88	Plasma-assisted MBE of GaN pn-junction Grown on Si(111) Substrate. <i>Chinese Journal of Chemical Physics</i> , <b>2010</b> , 23, 431-436	0.9	5
87	Performance improvement of large area GaN MSM photodiode with thin AlGa <sub>n</sub> surface layer. <i>Microelectronics International</i> , <b>2010</b> , 27, 140-142	0.8	9

86	Determination of the Al Composition of Al <sub>x</sub> Ga <sub>1-x</sub> N Thin Films By Means Of EDX and XRD Techniques <b>2010</b> ,		1
85	The effect of porosity on the properties of silicon solar cell. <i>Microelectronics International</i> , <b>2010</b> , 27, 117-120		11
84	Structural and optical properties of Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N quaternary alloys grown on sapphire substrates by molecular beam epitaxy. <i>Microelectronics International</i> , <b>2010</b> , 27, 148-153	0.8	1
83	Surface phonon polariton characteristics of In(0.04)Al(0.06)Ga(0.90)N/AlN/Al(2)O(3) heterostructure. <i>Optics Express</i> , <b>2010</b> , 18, 10354-9	3.3	4
82	Ohmic contacts properties of Ni/Ag metallization scheme on p-type GaN. <i>Journal of Non-Crystalline Solids</i> , <b>2010</b> , 356, 181-185	3.9	5
81	Effect of thermal annealing on the Ir/Ag contact to p-type GaN. <i>Journal of Non-Crystalline Solids</i> , <b>2010</b> , 356, 1863-1866	3.9	5
80	The growth of III-V nitrides heterostructure on Si substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , <b>2010</b> , 506, 343-346	5.7	14
79	ELECTRICAL PROPERTIES OF AlGa <sub>n</sub> /Ga <sub>n</sub> N HETEROSTRUCTURE FIELD-EFFECT TRANSISTORS (HFETs) WITH AND WITHOUT Mg-DOPED CARRIER CONFINEMENT LAYER. <i>International Journal of Nanoscience</i> , <b>2010</b> , 09, 263-267	0.6	
78	Sapphire surface polariton splitting due to resonance with aluminum nitride film phonon. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 210, 012027	0.3	4
77	High photoluminescence of silicon nanostructures synthesized by laser-induced etching. <i>Microelectronics International</i> , <b>2010</b> , 27, 45-48	0.8	1
76	Kramers-Kronig Analysis of Infrared Reflectance Spectra for Quaternary In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N Alloy <b>2010</b> ,		1
75	p-polarized infrared attenuated total reflection study of InN thin films grown on Si(111) substrate. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 191-193	2.5	2
74	Sm <sub>2</sub> O <sub>3</sub> gate dielectric on Si substrate. <i>Materials Science in Semiconductor Processing</i> , <b>2010</b> , 13, 303-314	4.3	41
73	Growth of zinc oxide nanoflowers by thermal evaporation method. <i>Physica B: Condensed Matter</i> , <b>2010</b> , 405, 2570-2572	2.8	36
72	Ultraviolet photoresponse properties of zinc oxide on type IIb diamond heterojunction. <i>Physica B: Condensed Matter</i> , <b>2010</b> , 405, 4123-4127	2.8	8
71	The structural and optical characterizations of ZnO synthesized using the Bottom-up growth method. <i>Physica B: Condensed Matter</i> , <b>2010</b> , 405, 2045-2048	2.8	28
70	Growth of high-quality ZnO nanowires without a catalyst. <i>Physica B: Condensed Matter</i> , <b>2010</b> , 405, 4216-4218	2.8	11
69	The effect of heat treatments on the properties of Ti/Pt heating elements for gas sensor applications. <i>Materials Science in Semiconductor Processing</i> , <b>2010</b> , 13, 199-204	4.3	2

68	A novel scheme for image encryption based on 2D piecewise chaotic maps. <i>Optics Communications</i> , <b>2010</b> , 283, 3259-3266	2	108
67	STRUCTURAL AND OPTICAL PROPERTIES OF LARGE-SCALE ZnO NANOWIRES AND NANOSHEETS PREPARED BY DRY THERMAL OXIDATION. <i>Surface Review and Letters</i> , <b>2009</b> , 16, 901-904	1.1	6
66	PREFERENTIAL ORIENTATION GROWTH OF AlN THIN FILMS ON Si(111) SUBSTRATES BY PLASMA-ASSISTED MOLECULAR BEAM EPITAXY. <i>Surface Review and Letters</i> , <b>2009</b> , 16, 925-928	1.1	3
65	INFLUENCE OF Al MONOLAYERS ON THE PROPERTIES OF AlN LAYERS ON Si (111). <i>Surface Review and Letters</i> , <b>2009</b> , 16, 99-103	1.1	6
64	SURFACE PHONON POLARITON MODES OF WURTZITE STRUCTURE InN SEMI-INFINITE CRYSTAL. <i>Surface Review and Letters</i> , <b>2009</b> , 16, 355-358	1.1	6
63	Surface and interface phonon polaritons of wurtzite GaN thin film grown on 6H-SiC substrate. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 241912	3.4	23
62	Structural and optical characteristics of porous GaN generated by electroless chemical etching. <i>Materials Letters</i> , <b>2009</b> , 63, 724-727	3.3	34
61	Structural Properties of Doped GaN on Si(111) Studied by X-Ray Diffraction Techniques. <i>Journal of Nondestructive Evaluation</i> , <b>2009</b> , 28, 125-130	2.1	20
60	Hash function based on hierarchy of 2D piecewise nonlinear chaotic maps. <i>Chaos, Solitons and Fractals</i> , <b>2009</b> , 42, 2405-2412	9.3	26
59	Strong coupling of sapphire surface polariton with aluminum nitride film phonon. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , <b>2009</b> , 373, 2382-2384	2.3	12
58	Porous Si(1 1 1) and Si(1 0 0) as an intermediate buffer layer for nanocrystalline InN films. <i>Journal of Alloys and Compounds</i> , <b>2009</b> , 479, L54-L58	5.7	29
57	GaN Schottky barrier photodiode on Si (111) with low-temperature-grown cap layer. <i>Journal of Alloys and Compounds</i> , <b>2009</b> , 481, L15-L19	5.7	15
56	High Al-content Al <sub>x</sub> Ga <sub>1-x</sub> N epilayers grown on Si substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , <b>2009</b> , 487, 24-27	5.7	45
55	InGaN/GaN laser diode characterization and quantum well number effect. <i>Chinese Optics Letters</i> , <b>2009</b> , 7, 226-230	2.2	2
54	STRUCTURAL AND OPTICAL FEATURES OF POROUS SILICON PREPARED BY ELECTROCHEMICAL ANODIC ETCHING. <i>Surface Review and Letters</i> , <b>2009</b> , 16, 93-97	1.1	2
53	Silicon Schottky barrier photodiodes with a thin AlN nucleation layer. <i>Microelectronics International</i> , <b>2009</b> , 26, 41-44	0.8	5
52	High-quality In <sub>0.47</sub> Ga <sub>0.53</sub> N/GaN heterostructure on Si(111) and its application to MSM detector. <i>Microelectronics International</i> , <b>2008</b> , 25, 3-8	0.8	7
51	LARGE AREA GaN METAL SEMICONDUCTOR METAL (MSM) PHOTODIODE USING A THIN LOW TEMPERATURE GaN CAP LAYER. <i>Journal of Nonlinear Optical Physics and Materials</i> , <b>2008</b> , 17, 59-69	0.8	3

50	p-GaN/n-Si HETEROJUNCTION PHOTODIODES. <i>Surface Review and Letters</i> , <b>2008</b> , 15, 699-703	1.1	3
49	Composition Dependence of Surface Phonon Polariton Mode in Wurtzite In <sub>x</sub> Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) Ternary Alloy. <i>Chinese Physics Letters</i> , <b>2008</b> , 25, 4378-4380	1.8	4
48	RF-MBE GROWTH OF GaN ON SAPPHIRE FOR GAS SENSING APPLICATION. <i>Journal of Nonlinear Optical Physics and Materials</i> , <b>2008</b> , 17, 435-442	0.8	
47	BARRIER HEIGHT ENHANCED GaN SCHOTTKY DIODES USING A THIN AlN SURFACE LAYER. <i>International Journal of Modern Physics B</i> , <b>2008</b> , 22, 5167-5173	1.1	4
46	ELECTRICAL RESISTANCE OF CRACK-FREE GaN/AlN HETEROSTRUCTURE GROWN ON Si(111). <i>Journal of Nonlinear Optical Physics and Materials</i> , <b>2008</b> , 17, 299-304	0.8	1
45	Effect of zinc on the growth mechanism of zinc oxide nanostructures in the nitrogen environment. <i>Journal Physics D: Applied Physics</i> , <b>2008</b> , 41, 055506	3	4
44	InGaN: An overview of the growth kinetics, physical properties and emission mechanisms. <i>Superlattices and Microstructures</i> , <b>2008</b> , 43, 1-23	2.8	178
43	Surface phonon polariton of wurtzite GaN thin film grown on $\bar{c}$ -plane sapphire substrate. <i>Solid State Communications</i> , <b>2008</b> , 145, 535-538	1.6	21
42	Investigation of the effects of porous layer on the electrical properties of Pt/n-GaN Schottky contacts. <i>Physica B: Condensed Matter</i> , <b>2008</b> , 403, 3105-3109	2.8	10
41	Polarized infrared reflectance study of wurtzite GaN thin film: The effects of angle of incidence on the optical phonon modes. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2007</b> , 25, 1557-1561	2.9	3
40	The study of Pt Schottky contact on porous GaN for hydrogen sensing. <i>Thin Solid Films</i> , <b>2007</b> , 515, 7337-7341	2.4	36
39	Investigation of structural and optical properties of nanoporous GaN film. <i>Applied Surface Science</i> , <b>2007</b> , 253, 7429-7434	6.7	20
38	Schottky diode based on porous GaN for hydrogen gas sensing application. <i>Applied Surface Science</i> , <b>2007</b> , 253, 9525-9528	6.7	46
37	Porous GaN prepared by UV assisted electrochemical etching. <i>Thin Solid Films</i> , <b>2007</b> , 515, 3469-3474	2.2	38
36	THE STUDY OF Pd SCHOTTKY CONTACT ON POROUS GaN FOR UV METAL/SEMICONDUCTOR/METAL (MSM) PHOTODETECTORS. <i>Journal of Nonlinear Optical Physics and Materials</i> , <b>2007</b> , 16, 497-503	0.8	1
35	Experimental and theoretical studies of surface phonon polariton of AlN thin film. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 081902	3.4	32
34	Surface phonon polariton mode of wurtzite structure Al <sub>x</sub> Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) thin films. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 081909	3.4	19
33	High carrier concentrations of n- and p-doped GaN on Si(111) by nitrogen plasma-assisted molecular-beam epitaxy. <i>Journal of Materials Research</i> , <b>2007</b> , 22, 2623-2630	2.5	13

32	Performance and optical characteristic of InGaN MQWs laser diodes. <i>Optics Express</i> , <b>2007</b> , 15, 2380-90	3.3	14
31	Response Mechanism of Pd-GaN Schottky Barriers Comparative to Pd-Si Gas Sensors. <i>Materials Science Forum</i> , <b>2006</b> , 517, 61-64	0.4	
30	The Study of Thermal Treatment on Electrical Properties at Cr/p-GaN. <i>Materials Science Forum</i> , <b>2006</b> , 517, 247-251	0.4	2
29	Pinning Fermi Level of p-GaN due to Three Different (Zr, Ti, and Cr) Metal Contact. <i>Materials Science Forum</i> , <b>2006</b> , 517, 262-266	0.4	1
28	Effects of Layer Thickness and Incident Angle Variations on DBR Reflectivity. <i>Materials Science Forum</i> , <b>2006</b> , 517, 29-32	0.4	
27	Structural and Optical Analysis of GaN Films Grown by Low-Pressure Metalorganic Chemical Vapor Deposition. <i>Materials Science Forum</i> , <b>2006</b> , 517, 5-8	0.4	
26	Effect of Thermal Treatment for Pd and PdSi Schottky Contacts on p-GaN. <i>Materials Science Forum</i> , <b>2006</b> , 517, 242-246	0.4	
25	A Chemical Sensor Based on AlGaIn. <i>Materials Science Forum</i> , <b>2006</b> , 517, 33-36	0.4	6
24	Investigation on Ag/Ti Ohmic Contacts to Si-Doped n-Type Al <sub>0.27</sub> Ga <sub>0.73</sub> N and the Effect of Post Annealing Treatments. <i>Materials Science Forum</i> , <b>2006</b> , 517, 281-286	0.4	
23	Crystallinity Studies of GaN/Si Films Grown by MOCVD at Various Substrate Temperatures Using XRD. <i>Materials Science Forum</i> , <b>2006</b> , 517, 69-72	0.4	
22	Design of DBR Mirrors for GaN Vertical Cavity Surface Emitting Laser. <i>Materials Science Forum</i> , <b>2006</b> , 517, 25-28	0.4	
21	Charge injection in polymer light-emitting diodes based on poly[(9,9-dioctylfluorenyl-2,7-diyl)-co-(1,4-phenylene)]. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 242109	3.4	1
20	Effect of hydrostatic pressure on the barrier height of Ni Schottky contacts on n-AlGaIn. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 022109	3.4	20
19	Nanoporous InN Films Synthesized using Photoelectrochemical (PEC) Wet Etching <b>2006</b> ,		2
18	Effects of Metal Work Function and Operating Temperatures on the Electrical Properties of Contacts to n-type GaN <b>2006</b> ,		2
17	Epitaxial GaN Film Grown at Low Temperature by Hydrogen-Plasma Assisted MOCVD. <i>Materials Science Forum</i> , <b>2006</b> , 517, 9-12	0.4	0
16	Optimization of InGaIn Based Light Emitting Diodes. <i>Materials Science Forum</i> , <b>2006</b> , 517, 195-201	0.4	
15	Electrical characteristics and thermal stability of Ti contact to p-GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1762-1766		2

14	AlGaIn metal-semiconductor-metal structure for pressure sensing applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 2287-2290		1
13	Large enhancement of GaN-UV light emission using silver mirror resonator. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 2022-2025		1
12	A comparative study of the electrical characteristics of metal-semiconductor-metal (MSM) photodiodes based on GaN grown on silicon. <i>Applied Surface Science</i> , <b>2005</b> , 249, 91-96	6.7	13
11	Dark current characteristics of thermally treated contacts on GaN-based ultraviolet photodetectors. <i>Microelectronic Engineering</i> , <b>2005</b> , 81, 262-267	2.5	12
10	Low applied bias for p-GaN electroluminescent devices. <i>Microelectronic Engineering</i> , <b>2005</b> , 81, 268-272	2.5	1
9	Innovative advances in LED technology. <i>Microelectronics Journal</i> , <b>2005</b> , 36, 129-137	1.8	142
8	Characteristics of low-temperature-grown GaN films on Si(111). <i>Solid State Communications</i> , <b>2005</b> , 133, 283-287	1.6	12
7	Crystallinity studies of GaN/Si films grown at different temperatures by infrared reflectance spectroscopy. <i>Materials Chemistry and Physics</i> , <b>2005</b> , 91, 404-408	4.4	7
6	Electrical characteristics of GaN-based metal-oxide-semiconductor (MOS) structures. <i>Microelectronic Engineering</i> , <b>2005</b> , 81, 201-205	2.5	4
5	Effects of post annealing treatments on the characteristics of ohmic contacts on n-type AlGaIn <b>2005</b> , 5739, 169		1
4	Thermal stability of contacts on AlGaIn-Based UV photodetectors <b>2004</b> , 5353, 151		
3	Microcrystalline GaN film grown on Si(1 0 0) and its application to MSM photodiode. <i>Materials Chemistry and Physics</i> , <b>2004</b> , 84, 369-374	4.4	10
2	Thermal stability of Ni/Ag contacts on p-type GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 2528-2532		5
1	PROPERTIES OF AMORPHOUS GAN GROWN ON SILICON. <i>International Journal of Modern Physics B</i> , <b>2002</b> , 16, 1086-1090	1.1	6